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- High-Performance Static CMOS Technology
- TMS470R1x 16/32-Bit RISC Core (ARM7TDMI™)
  - 60-MHz System Clock (Pipeline Mode)
  - Independent 16/32-Bit Instruction Set
  - Open Architecture With Third-Party Support
  - Built-In Debug Module
- Integrated Memory (VF48C only)
  - 1M-Byte Program Flash
    - -Two Banks With 16 Contiguous Sectors
  - 64K-Byte Static RAM (SRAM)
  - Memory Security Module (MSM)
  - JTAG Security Module
- Integrated Memory (VF48B only)
  - 768K-Byte Program Flash
    - Two Banks With 12 Contiguous Sectors
  - 48K-Byte Static RAM (SRAM)
  - Memory Security Module (MSM)
  - JTAG Security Module
- Operating Features
  - Low-Power Modes: STANDBY and HALT
  - Industrial/Automotive Temperature Ranges
- 470+ System Module
  - 32-Bit Address Space Decoding
  - Bus Supervision for Memory/Peripherals
  - Digital Watchdog (DWD) Timer
  - Analog Watchdog (AWD) Timer
  - Enhanced Real-Time Interrupt (RTI)
  - Interrupt Expansion Module (IEM)
  - System Integrity and Failure Detection
  - ICE Breaker
- Direct Memory Access (DMA) Controller
  - 32 Control Packets and 16 Channels
- Frequency-Modulated Zero-Pin Phase-Locked Loop (FM<sub>Z</sub>PLL)-Based Clock Module With Prescaler
  - Multiply-by-8 Internal FM<sub>2</sub>PLL Option
  - ZPLL Bypass Mode
- Twelve Communication Interfaces:
  - Two Serial Peripheral Interfaces (SPIs)
    - 255 Programmable Baud Rates
  - Three Serial Communication Interfaces (SCIs)
    - 2<sup>24</sup> Selectable Baud Rates
    - Asynchronous/Isosynchronous Modes

- Two High-End CAN Controllers (HECC)
  - 32-Mailbox Capacity
  - Fully Compliant With CAN Protocol, Version 2.0B
- Five Inter-Integrated Circuit (I2C) Modules
  - Multi-Master and Slave Interfaces
  - Up to 400 Kbps (Fast Mode)
  - 7- and 10-Bit Address Capability
- High-End Timer Lite (HET)
  - 12 Programmable I/O Channels:
    - 12 High-Resolution Pins
  - High-Resolution Share Feature (XOR)
  - High-End Timer RAM
    - 64-Instruction Capacity
- External Clock Prescale (ECP) Module
  - Programmable Low-Frequency External Clock (CLK)
- 12-Channel 10-Bit Multi-Buffered ADC (MibADC)
  - 64-Word FIFO Buffer
  - Single- or Continuous-Conversion Modes
  - 1.55 μs Minimum Sample and Conversion Time
  - Calibration Mode and Self-Test Features
- Flexible Interrupt Handling
- Expansion Bus Module (EBM)
  - Supports 8- and 16-Bit Expansion Bus Memory Interface Mappings
  - 42 I/O Expansion Bus Pins
- 46 Dedicated General-Purpose I/O (GIO) Pins and 47 Additional Peripheral I/Os
- Sixteen External Interrupts
- Compatible ROM Device (Planned)
- On-Chip Scan-Base Emulation Logic, IEEE Standard 1149.1<sup>(1)</sup> (JTAG) Test-Access Port
- 144-Pin Plastic Low-Profile Quad Flatpack (PGE Suffix)
- Development System Support Tools Available
  - Code Composer Studio<sup>™</sup> Integrated Development Environment (IDE)
  - HET Assembler and Simulator
  - Real-Time In-Circuit Emulation
  - Flash Programming



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of TexasInstruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

Code Composer Studio is a trademark of Texas Instruments.

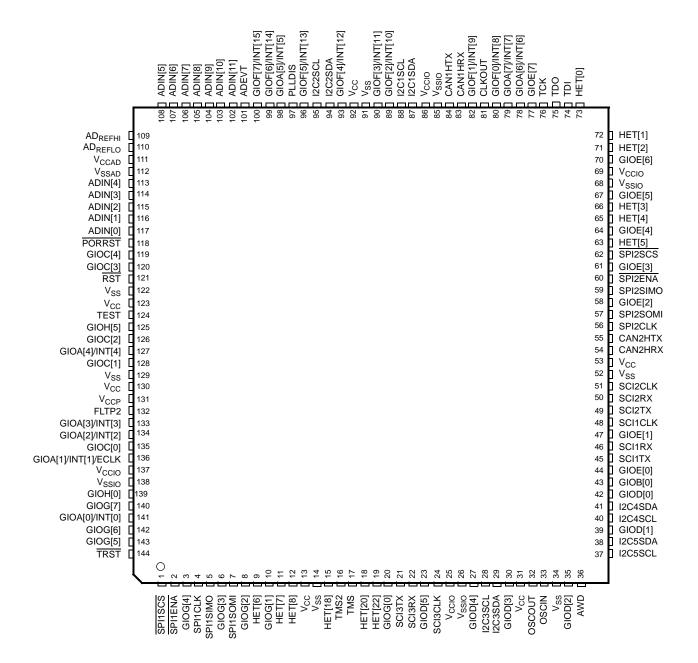
ARM7TDMI is a trademark of Advanced RISC Machines Limited (ARM).

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1 The test-access port is compatible with the IEEE Standard 1149.1-1990, IEEE Standard Test-Access Port and Boundary Scan Architecture specification. Boundary scan is not supported on this device.



#### TMS470R1VF48C/TMS470R1VF48B 144-PIN PGE PACKAGE (TOP VIEW)





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## description

The VF48x<sup>(2)</sup> devices are members of the Texas Instruments TMS470R1x family of general-purpose 16/32-bit reduced instruction set computer (RISCIIers. The VF48x microcontroller offers high performance utilizing the high-speed ARM7TDMI 16/32-bit RISC central processing unit (CPU), resulting in a high instruction throughput while maintaining greater code efficiency. The ARM7TDMI 16/32-bit RISC CPU views memory as a linear collection of bytes numbered upwards from zero. The VF48x uses the big-endian format where the most significant byte of a word is stored at the lowest numbered byte and the least significant byte at the highest numbered byte.

High-end embedded control applications demand more performance from their controllers while maintaining low costs. The VF48x RISC core architecture offers solutions to these performance and cost demands while maintaining low power consumption.

The VF48x devices contain the following:

- ARM7TDMI 16/32-Bit RISC CPU
- TMS470R1x system module (SYS) with 470+ enhancements
- 1M-byte flash (VF48C only)
- 768K-byte flash (VF48B only)
- 64K-byte SRAM (VF48C only)
- 48K-byte SRAM (VF48B only)
- Frequency-modulated zero-pin phase-locked loop (FM<sub>7</sub>PLL) clock module
- Digital watchdog (DWD) timer
- Analog watchdog (AWD) timer
- Enhanced real-time interrupt (RTI) module
- Interrupt expansion module (IEM)
- Memory security module (MSM)
- JTAG security module
- Two serial peripheral interface (SPI) modules
- Three serial communications interface (SCI) modules
- Two high-end CAN controllers (HECC)
- Five inter-integrated circuit (I2C) modules
- 10-bit multi-buffered analog-to-digital converter (MibADC), with 12 input channels
- High-end timer lite (HET) controlling 12 I/Os
- External Clock Prescale (ECP)
- Expansion Bus Module (EBM)
- Up to 93 I/O pins

The functions performed by the 470+ system module (SYS) include:

- Address decoding
- Memory protection
- Memory and peripherals bus supervision
- Reset and abort exception management
- Prioritization for all internal interrupt sources
- Device clock control
- Parallel signature analysis (PSA)

The enhanced real-time interrupt (RTI) module on the VF48x has the option to be driven by the oscillator clock. The digital watchdog (DWD) is a 25-bit resettable decrementing counter that provides a system reset when the watchdog counter expires. This data sheet includes device-specific information such as memory and peripheral select assignment, interrupt priority, and a device memory map. For a more detailed functional description of the SYS module, see the *TMS470R1x System Module Reference Guide* (literature number SPNU189).

2 Throughout the remainder of this document, the TMS470R1VF48C and TMS740R1VF48B device names, where generic, will be referred to as either VF48C/VF48B or VF48x; and where unique, by either the full device name or VF48C or VF48B.



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## description (continued)

The VF48x memory includes general-purpose SRAM supporting single-cycle read/write accesses in byte, half-word, and word modes.

The flash memory on this device is a nonvolatile, electrically erasable and programmable memory implemented with a 32-bit-wide data bus interface. The flash operates with a system clock frequency of up to 24 MHz. When in pipeline mode, the flash operates with a system clock frequency of up to 60 MHz. For more detailed information on the flash, see the flash section of this data sheet and the *TMS470R1x F05 Flash Reference Guide* (literature number SPNU213).

The memory security module (MSM) and the JTAG security module prevent unauthorized access and visibility to on-chip memory, thereby preventing reverse engineering or manipulation of proprietary code. For more detailed information, see the *TMS470R1x Memory Security Module Reference Guide* (literature number SPNU246) and the *TMS470R1x JTAG Security Module Reference Guide* (literature number SPNU245).

The VF48x device has twelve communication interfaces: two SPIs, three SCIs, two HECCs, and five I2Cs. The SPI provides a convenient method of serial interaction for high-speed communications between similar shift-register type devices. The SCI is a full-duplex, serial I/O interface intended for asynchronous communication between the CPU and other peripherals using the standard non-return-to-zero (NRZ) format. The HECC uses a serial, multimaster communication protocol that efficiently supports distributed real-time control with robust communication rates of up to 1 megabit per second (Mbps). These CAN peripherals are ideal for applications operating in noisy and harsh environments (e.g., automotive and industrial fields) that require reliable serial communication or multiplexed wiring. The I2C module is a multi-master communication module providing an interface between the VF48x microcontroller and an I2C-compatible device via the I2C serial bus. The I2C supports both 100 Kbps and 400 Kbps speeds. For more detailed functional information on the SPI, SCI, and CAN peripherals, see the specific reference guides (literature numbers SPNU195, SPNU196, and SPNU197). For more detailed functional information on the I2C, see the *TMS470R1x Inter-Integrated Circuit (I2C) Reference Guide* (literature number SPNU223).

The HET is an advanced intelligent timer that provides sophisticated timing functions for real-time applications. The timer is software-controlled, using a reduced instruction set, with a specialized timer micromachine and an attached I/O port. The HET can be used for compare, capture, or general-purpose I/O. It is especially well suited for applications requiring multiple sensor information and drive actuators with complex and accurate time pulses. The HET used in this device is the high-end timer lite. It has fewer I/Os than the usual 32 in a standard HET. For more detailed functional information on the HET, see the *TMS470R1x High-End Timer (HET) Reference Guide* (literature number SPNU199). The VF48x HET peripheral contains the XOR-share feature. This feature allows two adjacent HET high- resolution channels to be XORed together, making it possible to output smaller pulses than a standard HET. For more detailed information on the HET XOR-share feature, see the *TMS470R1x High-End Timer (HET) Reference Guide* (literature number SPNU199).

The VF48x device has one 10-bit-resolution, sample-and-hold MibADC. Each of the MibADC channels can be converted individually or can be grouped by software for sequential conversion sequences. There are three separate groupings, two of which can be triggered by an external event. Each sequence can be converted once when triggered or configured for continuous conversion mode. For more detailed functional information on the MibADC, see the TMS470R1x Multi-Buffered Analog-to-Digital Converter (MibADC) Reference Guide (literature number SPNU206).



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### description (continued)

The frequency-modulated zero-pin phase-locked loop (FM<sub>Z</sub>PLL) clock module contains a phase-locked loop, a clock-monitor circuit, a clock-enable circuit, and a prescaler (with prescale values of 1–8). The function of the FM<sub>Z</sub>PLL is to multiply the external frequency reference to a higher frequency for internal use. The FM<sub>Z</sub>PLL provides ACLK to the system (SYS) module. The SYS module subsequently provides system clock (SYSCLK), real-time interrupt clock (RTICLK), CPU clock (MCLK), and peripheral interface clock (ICLK) to all other VF48x device modules. For more detailed functional information on the FM<sub>Z</sub>PLL, see the *TMS470R1x Frequency-Modulated Phase-Locked Loop (FMPLL) Clock Module Reference Guide* (literature number SPNU221).

#### **NOTE**

ACLK should not be confused with the MibADC internal clock, ADCLK. ACLK is the continuous system clock from an external resonator/crystal reference.

The expansion bus module (EBM) is a standalone module that supports the multiplexing of the GIO functions and the expansion bus interface. For more information on the EBM, see the *TMS470R1x Expansion Bus Module (EBM) Reference Guide* (literature number SPNU222).

The VF48x device also has an external clock prescaler (ECP) module that when enabled, outputs a continuous external clock (ECLK) on a specified GIO pin. The ECLK frequency is a user-programmable ratio of the peripheral interface clock (ICLK) frequency. For more detailed functional information on the ECP, see the TMS470R1x External Clock Prescaler (ECP) Reference Guide (literature number SPNU202).



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## device characteristics

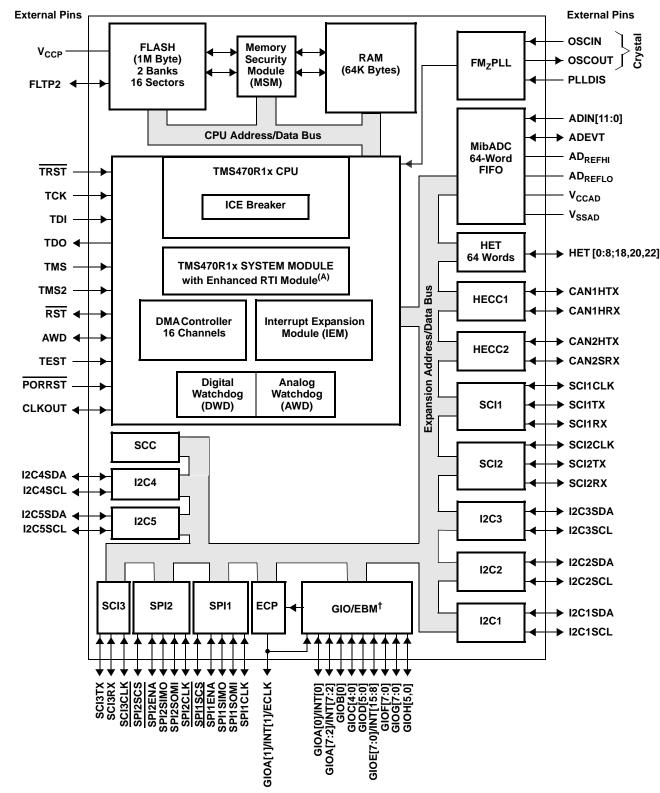
The VF48x device is a derivative of the F05 system emulation device SE470R1VB8AD. Table 1 identifies all the characteristics of the VF48x device except the SYSTEM and CPU, which are generic.

**Table 1. Device Characteristics** 

CHARACTERISTICS	DEVICE DESCRIPTION TMS470R1VF48X	COMMENTS FOR VF48X
	MEI	MORY
For the number of memory select	ts on this device, see the Memory Se	election Assignment table (Table 2).
	Pipeline/Non-Pipeline	Flash is pipeline-capable.
INTERNAL MEMORY	1M-Byte flash (VF48C only) 768K-byte flash (VF48B only) 64K-Byte SRAM (VF48C only) 48K-byte SRAM (VF48B only)	The VF48C RAM is implemented in one 64K array selected by two memory-select signals (see the Memory Selection Assignment table, Table 2).  The VF48B RAM is implemented in one 48K array selected by two
	Memory Security Module (MSM) JTAG Security Module	memory-select signals (see the Memory Selection Assignment table, Table 2).
	PERIP	HERALS
		ot Priority Table (Table 5). And for the 1K peripheral address ranges and and Flash Base Addresses table (Table 3).
CLOCK	FM <sub>Z</sub> PLL	Frequency-modulated zero-pin PLL has no external loop filter pins.
Expansion Bus	ЕВМ	Expansion bus module with 42 pins. Supports 8- and 16-bit memories. See Table 6 for details.
GENERAL-PURPOSE I/Os	46 I/O	Port A has 8 external pins, Port B has only 1 external pin, Port C has 5 external pins, Port D has 6 external pins, Ports E, F, and G each have 8 external pins, and Port H has 2 external pins.
ECP	YES	
SCI	3 (3-pin)	
CAN (HECC and/or SCC)	2 HECC	Two high-end CAN controllers
SPI (5-pin, 4-pin or 3-pin)	2 (5-pin)	
I2C	5	
HET with XOR Share	12 I/O	The high-resolution (HR) SHARE feature allows even-numbered HR pins to share the next higher odd-numbered HR pin structures. This HR sharing is independent of whether or not the odd pin is available externally. If an odd pin is available externally and <i>shared</i> , then the odd pin can only be used as a general-purpose I/O. For more information on HR SHARE, see the TMS470R1x High-End Timer (HET) Reference Guide (literature number SPNU199).
HET RAM	64-Instruction Capacity	
MibADC	10-bit, 12-channel 64-word FIFO	Both the logic and registers for a full 16-channel MibADC are present.
CORE VOLTAGE	1.8 V	
I/O VOLTAGE	3.3 V	
PINS	144	
PACKAGES	PGE	

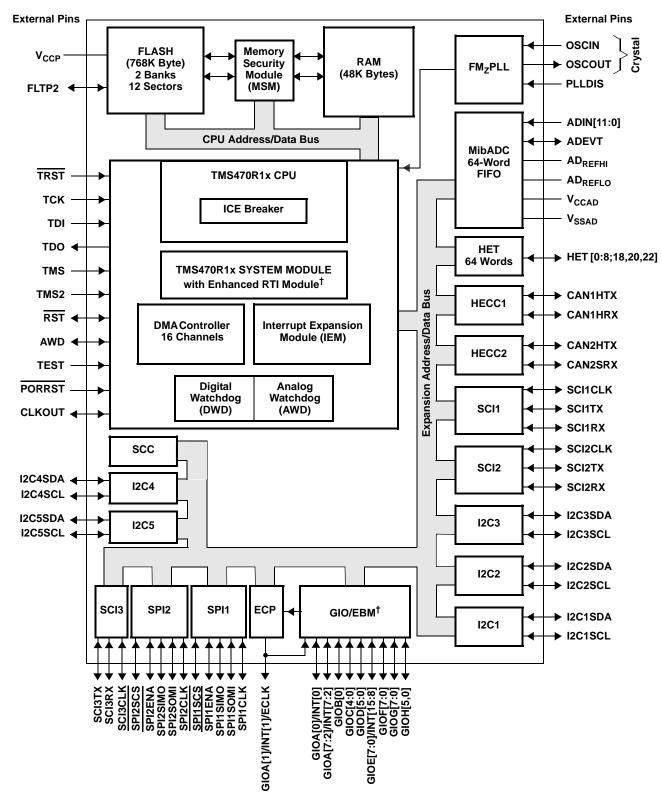


## functional block diagram (VF48C)



A. The enhanced RTI module is the system module with two extra bits to disable the FM<sub>Z</sub>PLL while in STANDBY mode.

## functional block diagram (VF48B)



A. The enhanced RTI module is the system module with two extra bits to disable the FM<sub>Z</sub>PLL while in STANDBY mode.



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## **Terminal Functions**

TERMINAI NAME	PIN NO.	INPUT VOLT- AGE <sup>(1)(2)</sup>	OUTPUT CURRENT <sup>(1)(2)</sup>	INTERNAL PULLUP/ PULL- DOWN <sup>(3)</sup>	DESCRIPTION
			L	HIGH-END	TIMER (HET)
HET[0]	73				
HET[1]	72				
HET[2]	71				Timer input capture or output compare. The HET[8:0,18,20,22] applicable
HET[3]	66				pins can be programmed as general-purpose input/output (GIO) pins. All are high-resolution pins.
HET[4]	65				are riigit-resolution pins.
HET[5]	63	221/	2	IPD	The high-resolution (HR) SHARE feature allows even HR pins to share
HET[6]	9	3.3-V	2mA -z	(20 μΑ)	the next higher odd HR pin structures. This HR sharing is independent of
HET[7]	11				whether or not the odd pin is available externally. If an odd pin is available
HET[8]	12				externally and <i>shared</i> , then the odd pin can only be used as a general-purpose I/O. For more information on HR SHARE, see the <i>TMS470R1x</i>
HET[18]	15				High-End Timer (HET) Reference Guide (literature number SPNU199).
HET[20]	18				
HET[22]	19				
	HIGH-END CAN CONTROLLER (HECC)				
CAN1HRX	83	5V tolerant	4mA		HECC1 receive pin or GIO pin
CAN1HTX	84	3.3-V	2mA -z	IPU (20 μA)	HECC1 transmit pin or GIO pin
CAN2HRX	54	5V tolerant	4mA		HECC2 receive pin or GIO pin
CAN2HTX	55	3.3-V	2mA -z	IPU (20 μA)	HECC2 transmit pin or GIO pin
			STAN	DARD CAN	CONTROLLER (SCC)
CANSRX	-	5V tolerant	4mA		SCC receive pin. The CANSRX signal is only connected to the pad and not to a package pin. For reduced power consumption in low power mode, CANSRX should be driven output LOW.
CANSTX	-	3.3-V	2mA -z	IPU (20 μA)	SCC transmit pin. The CANSTX signal is only connected to the pad and not to a package pin. For reduced power consumption in low power mode, CANSTX should be driven output LOW.
			G	ENERAL-PU	RPOSE I/O (GIO)
GIOA[0]/INT[0]	141				
GIOA[1]/INT[1]/ ECLK	136				General-purpose input/output pins. GIOA[7:0]/INT[7:0] are interrupt-
GIOA[2]/INT[2]	134				capable pins.
GIOA[3]/INT[3]	133	5V tolerant	4mA		GIOA[1]/INT[1]/ECLK pin is multiplexed with the external clock-out
GIOA[4]/INT[4]	127				function of the external clock prescale (ECP) module.
GIOA[5]/INT[5]	98				. , ,
GIOA[6]/INT[6]	78				
GIOA[7]/INT[7]	79				
GIOB[0]	43				
GIOC[0]	135				GIOB[0], GIOC[4:0], GIOD[5:0], GIOE[7:0:], GIOF[7:0], GIOG[7:0], AND
GIOC[1]	128	3.3-V	2mA -z	IPD (22	GIOH[5,0] are multiplexed with the expansion bus module.
GIOC[2]	126	0.0 .		(20 μA)	SaaTabla 6
GIOC[3]	120				SeeTable 6.
GIOC[4]	119				

<sup>1</sup> PWR = power, GND = ground, REF = reference voltage, NC = no connect



<sup>2</sup> All I/O pins, except RST, are configured as inputs while PORRST is low and immediately after PORRST goes high.

<sup>3</sup> IPD = internal pulldown, IPU = internal pullup (all internal pullups and pulldowns are active on input pins, independent of the PORRST state.)

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TERMINAL NAME	PIN	INPUT VOLT-	OUTPUT CURRENT <sup>(1)(2)</sup>	INTERNAL PULLUP/ PULL-	DESCRIPTION
NAME	NO.	AGE <sup>(1)(2)</sup>		DOWN <sup>(3)</sup>	
			GENERAL-	PURPOSE I/	O (GIO) (CONTINUED)
GIOD[0]	42				
GIOD[1]	39				
GIOD[2]	35				
GIOD[3]	30				
GIOD[4]	27				
GIOD[5]	23				
GIOE[0]	44				
GIOE[1]	47				
GIOE[2]	58				
GIOE[3]	61				
GIOE[4]	64				
GIOE[5]	67				
GIOE[6]	70				
GIOE[7]	77				GIOB[0], GIOC[4:0], GIOD[5:0], GIOE[7:0:], GIOF[7:0], GIOG[7:0],
GIOF[0]/INT[8]	80				AND GIOH[5,0] are multiplexed with the expansion bus module.
GIOF[1]/INT[9]	82	3.3-V	2mA -z	IPD	
GIOF[2]/INT[10]	89	3.5°V	2111/4 -2	(20 μΑ)	GIOF[7:0]/INT[15:8] are interrupt capable pins.
GIOF[3]/INT[11]	90				Con Table C
GIOF[4]/INT[12]	93				See Table 6.
GIOF[5]/INT[13]	96				
GIOF[6]/INT[14]	99				
GIOF[7]/INT[15]	100				
GIOG[0]	20				
GIOG[1]	10				
GIOG[2]	8				
GIOG[3]	6				
GIOG[4]	3				
GIOG[5]	143				
GIOG[6]	142				
GIOG[7]	140				
GIOH[0]	139				
GIOH[5]	125				

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TERMINAL NAME	PIN NO.	INPUT VOLT- AGE <sup>(1)(2)</sup>	OUTPUT CURRENT <sup>(1)(2)</sup>	INTERNAL PULLUP/ PULL- DOWN <sup>(3)</sup>	DESCRIPTION	
		MULTI-BUF	FERED ANALOG	G-TO-DIGITAL	CONVERTER (MibADC)	
ADEVT	101		2mA -z	IPD (20 μA)	MibADC event input. Can be programmed as a GIO pin.	
ADIN[0]	117					
ADIN[1]	116					
ADIN[2]	115					
ADIN[3]	114					
ADIN[4]	113					
ADIN[5]	108	3.3-V			Mih ADC analog input pina	
ADIN[6]	107				MibADC analog input pins	
ADIN[7]	106					
ADIN[8]	105					
ADIN[9]	104					
ADIN[10]	103					
ADIN[11]	102					
AD <sub>REFHI</sub>	109	3.3-V REF			MibADC module high-voltage reference input	
AD <sub>REFLO</sub>	110	GND REF			MibADC module low-voltage reference input	
V <sub>CCAD</sub>	111	3.3-V PWR			MibADC analog supply voltage	
V <sub>SSAD</sub>	112	GND			MibADC analog ground reference	
			SERIAL PERIPH	ERAL INTERF	FACE 1 (SPI1)	
SPI1CLK	4				SPI1 clock. SPI1CLK can be programmed as a GIO pin.	
SPI1ENA	2				SPI1 chip enable. Can be programmed as a GIO pin.	
SPI1SCS	1	->			SPI1 slave chip select. Can be programmed as a GIO pin.	
SPI1SIMO	5	5V tolerant	4mA		SPI1 data stream. Slave in/master out. Can be programmed as a GIO pin.	
SPI1SOMI	7				SPI1 data stream. Slave out/master in. Can be programmed as a GIO pin.	
			SERIAL PERIPH	ERAL INTERF	FACE 2 (SPI2)	
SPI2CLK	56				SPI2 clock. Can be programmed as a GIO pin.	
SPI2ENA	60				SPI2 chip enable. Can be programmed as a GIO pin.	
SPI2SCS	62				SPI2 slave chip select. Can be programmed as a GIO pin.	
SPI2SIMO	59	5V tolerant	4mA		SPI2 data stream. Slave in/master out. Can be programmed as a GIO pin.	
SPI2SOMI	57				SPI2 data stream. Slave out/master in. Can be programmed as a GIO pin.	
			INTER-INTEG	RATED CIRCU	JIT 1 (I2C1)	
I2C1SDA	87	5V tolerant	4mA		I2C1 serial data pin or GIO pin	
I2C1SCL	88	JV IUICIAIII	4111/4		I2C1 serial clock pin or GIO pin	
			INTER-INTEG	RATED CIRCU	JIT 2 (I2C2)	
I2C2SDA	94	5V tolerant	4mA		I2C2 serial data pin or GIO pin	
I2C2SCL	95	ov tolerailt	TIIIA		I2C2 serial clock pin or GIO pin	



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TERMIN	TERMINAL INPUT OUTPUT INTERNAL				
I EKWIIN.	PIN	VOLT-	OUTPUT	PULLUP/	DESCRIPTION
NAME	NO.	$AGE^{(1)(2)}$	CURRENT <sup>(1)(2)</sup>	PULLDOWN <sup>(3)</sup>	DESCRIPTION
			INT	ER-INTEGRATE	ED CIRCUIT 3 (I2C3)
I2C3SDA	29				I2C3 serial data pin or GIO pin
I2C3SCL	28	5V tolerant	4mA		I2C3 serial clock pin or GIO pin
			INT	ER-INTEGRATE	D CIRCUIT 4 (I2C4)
I2C4SDA	41				I2C4 serial data pin or GIO pin
I2C4SCL	40	5V tolerant	4mA		I2C4 serial clock pin or GIO pin
	I		INT	ER-INTEGRATE	D CIRCUIT 5 (I2C5)
I2C5SDA	38	51// 1			I2C5 serial data pin or GIO pin
I2C5SCL	37	5V tolerant	4mA		I2C5 serial clock pin or GIO pin
	I	FRE	QUENCY-MODU	LATED ZERO-P	PIN PHASE-LOCKED LOOP (FM <sub>Z</sub> PLL)
OSCIN 33 1.8-V Crystal connection pin or external clock input					
OSCOUT	32		2mA		External crystal connection pin
					Enable/disable the FM <sub>Z</sub> PLL. The FM <sub>Z</sub> PLL can be bypassed and the
DI I DIC	07	221/		IPD	oscillator becomes the system clock. If not in bypass mode, TI
PLLDIS	97	3.3-V		(20 μΑ)	recommends that this pin be connected to ground or pulled down to
					ground by an external resistor.
			1		DNS INTERFACE 1 (SCI1)
SCI1CLK	48	3.3-V	2mA -z	IPD (20 μA)	SCI1 clock. SCI1CLK can be programmed as a GIO pin.
SCI1RX	46	5V tolerant	4mA		SCI1 data receive. SCI1RX can be programmed as a GIO pin.
SCI1TX	45	3.3-V	2mA -z	IPU (20 μA)	SCI1 data transmit. SCI1TX can be programmed as a GIO pin.
			SERIAL (	COMMUNICATION	DNS INTERFACE 2 (SCI2)
SCI2CLK	51	3.3-V	2mA -z	IPD(20 μA)	SCI2 clock. SCI2CLK can be programmed as a GIO pin.
SCI2RX	50	5V tolerant	4mA		SCI2 data receive. SCI2RX can be programmed as a GIO pin.
SCI2TX	49	3.3-V	2mA -z	IPU (20 μA)	SCI2 data transmit. SCI2TX can be programmed as a GIO pin.
			SERIAL (	COMMUNICATION	DNS INTERFACE 3 (SCI3)
SCI3CLK	24	3.3-V	2mA -z	IPD (20 μA)	SCI3 clock. SCI3CLK can be programmed as a GIO pin.
SCI3RX	22	5V tolerant	4mA		SCI3 data receive. SCI3RX can be programmed as a GIO pin.
SCI3TX	21	3.3-V	2mA -z	IPU (20 μA)	SCI3 data transmit. SCI3TX can be programmed as a GIO pin.
				SYSTEM MC	DDULE (SYS)
CLKOUT	81	3.3-V	8mA		Bidirectional pin. CLKOUT can be programmed as a GIO pin or the output of SYSCLK, ICLK, or MCLK.
PORRST	118	3.3-V		IPD (20 μA)	Input master chip power-up reset. External V <sub>CC</sub> monitor circuitry must assert a power-on reset.
RST	121	3.3-V	4mA	IPU (20 μA)	Bidirectional reset. The internal circuitry can assert a reset, and an external system reset can assert a device reset. On this pin, the output buffer is implemented as an open drain (drives low only). To ensure an external reset is not arbitrarily generated, TI recommends that an external pullup resistor be connected to this pin.
			WATCH	DOG/REAL-TIM	E INTERRUPT (WD/RTI)
AWD	36	3.3-V	8mA		Analog watchdog reset. The AWD pin provides a system reset if the WD KEY is not written in time by the system, providing an external RC network circuit is connected. If the user is not using AWD, TI recommends that this pin be connected to ground or pulled down to ground by an external resistor.  For more details on the external RC network circuit, see the TMS470R1x System Module Reference Guide (literature number SPNU189).

<sup>1</sup> PWR = power, GND = ground, REF = reference voltage, NC = no connect

<sup>3</sup> IPD = internal pulldown, IPU = internal pullup (all internal pullups and pulldowns are active on input pins, independent of the PORRST state.)



<sup>2</sup> All I/O pins, except  $\overline{RST}$ , are configured as inputs while  $\overline{PORRST}$  is low and immediately after  $\overline{PORRST}$  goes high.

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TERMINAL INDUT INTERN		INTERNAL	AL			
NAME	PIN NO.	INPUT VOLT- AGE <sup>(1)(2)</sup>	OUTPUT CURRENT <sup>(1)(2)</sup>	PULLUP/ PULL- DOWN <sup>(3)</sup>	DESCRIPTION	
				TEST/DI	EBUG (T/D)	
тск	76	3.3-V		IPD (20 μA)	Test clock. TCK controls the test hardware (JTAG).	
TDI	74	3.3-V	8mA	IPU (20 μA)	Test data in. TDI inputs serial data to the test instruction register, test data register, and programmable test address (JTAG).	
TDO	75		8mA	IPD (20 μA)	Test data out. TDO outputs serial data from the test instruction register, test data register, identification register, and programmable test address (JTAG).	
TEST	124			IPD (20 μA)	Test enable. Reserved for internal use only. TI recommends that this pin be connected to ground or pulled down to ground by an external resistor.	
TMS	17		8mA	IPU (20 μA)	Serial input for controlling the state of the CPU test access port (TAP) controller (JTAG).	
TMS2	16	3.3-V	8mA	IPU (20 μA)	Serial input for controlling the second TAP. TI recommends that this pin be connected to $V_{\text{CCIO}}$ or pulled up to $V_{\text{CCIO}}$ by an external resistor.	
TRST	144			IPD (20 μA)	Test hardware reset to TAP1 and TAP2. IEEE Standard 1149-1 (JTAG) Boundary-Scan Logic. TI recommends that this pin be pulled down to ground by an external resistor.	
	FLASH					
FLTP2	132	NC	NC		Flash test pad 2. For proper operation, this pin must not be connected [no connect (NC)].	
$V_{CCP}$	131	3.3-V PWR			Flash external pump voltage (3.3 V)	
	•		SI	JPPLY VOLT	AGE CORE (1.8 V)	
V <sub>CC</sub>	13 31 53 92 123 130	1.8-V PWR			Core logic supply voltage	
			SUPF	PLY VOLTAG	E DIGITAL I/O (3.3 V)	
V <sub>ccio</sub>	25 69 86 137	3.3-V PWR			Digital I/O supply voltage	
				SUPPLY GI	ROUND CORE	
V <sub>SS</sub>	14 34 52 91 122 129	GND			Core supply ground reference	
			S	UPPLY GRO	UND DIGITAL I/O	
V <sub>ssio</sub>	26 68 85 138	GND			Digital I/O supply ground reference	

<sup>1</sup> PWR = power, GND = ground, REF = reference voltage, NC = no connect

<sup>3</sup> IPD = internal pulldown, IPU = internal pullup (all internal pullups and pulldowns are active on input pins, independent of the PORRST state.)

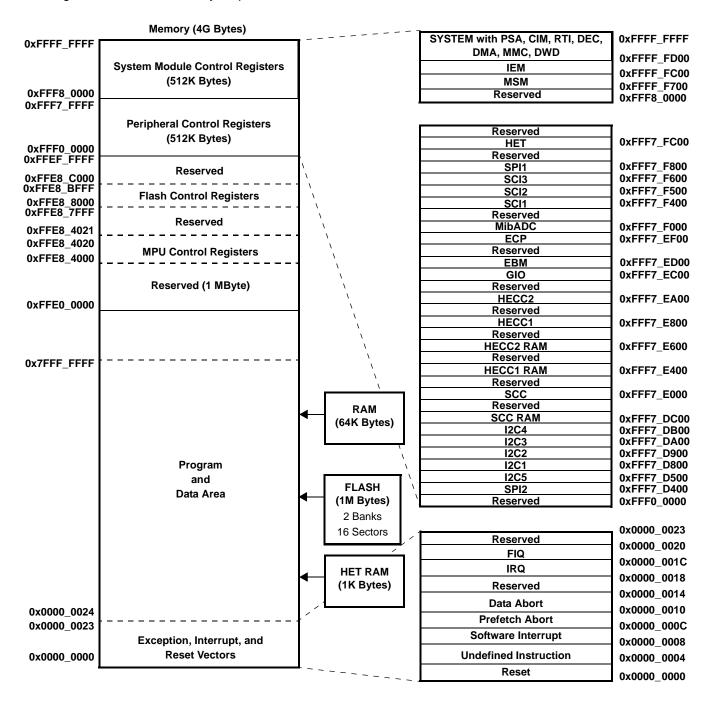


<sup>2</sup> All I/O pins, except  $\overline{RST}$ , are configured as inputs while  $\overline{PORRST}$  is low and immediately after  $\overline{PORRST}$  goes high.

#### VF48X DEVICE-SPECIFIC INFORMATION

### memory

Figure 1 shows the memory map of the VF48C device.



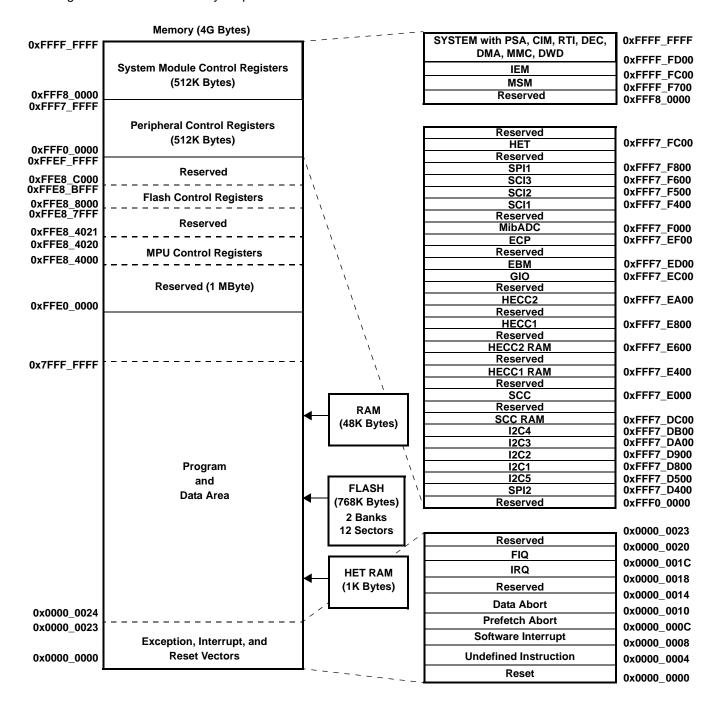
- A. Memory addresses are configurable by the system (SYS) module within the range of 0x0000\_0000 to 0xFFE0\_0000.
- B. The CPU registers are not a part of the memory map.

Figure 1. TMS470R1VF48C Memory Map



## memory (continued)

Figure 2 shows the memory map of the VF48B device.



- A. Memory addresses are configurable by the system (SYS) module within the range of 0x0000\_0000 to 0xFFE0\_0000.
- B. The CPU registers are not a part of the memory map.

Figure 2. TMS470R1VF48B Memory Map



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## memory selects

Memory selects allow the user to address memory arrays (i.e., flash, RAM, and HET RAM) at user-defined addresses. Each memory select has its own set (low and high) of memory base address registers (MFBAHRx and MFBALRx) that, together, define the array's starting (base) address, size, and protection.

The base address of each memory select is configurable to any memory address boundary that is a multiple of the decoded block size. The decoded block size for the flash memory on this device is 0x00400000. For more information on how to control and configure these memory select registers, see the bus structure and memory sections of the *TMS470R1x System Module Reference Guide* (literature number SPNU189).

For the memory selection assignments and the memory selected, see Table 2.

MEMORY **MEMORY MEMORY SELECTED** STATIC MEM MPU **MEMORY BASE ADDRESS REGISTER** MSM **SELECT** SIZE<sup>(1)</sup> **CTL REGISTER** (ALL INTERNAL) 1M (VF48C) NO YES MFBAHR0 and MFBALR0 0 (fine) FLASH/ROM 768 K 1 (fine) FLASH/ROM NO YES MFBAHR1 and MFBALR1 (VF48B) YES YES 2 (fine) RAM MFBAHR2 and MFBALR2 64K<sup>(2)</sup> (VF48C) 3 (fine) RAM 48K<sup>(2)</sup> YES YES MFBAHR3 and MFBALR3 (VF48B) HET RAM 1K NO MFBAHR4 and MFBALR4 4 (fine) NO SMCR1 128MB (x8) CS[5]/GIOC[3] NO NO MCBAHR2 and MCBALR2 SMCR5 5 (coarse) 1MB (x16) 128MB (x8) NO 6 (coarse) CS[6]/GIOC[4] NO MCBAHR3 and MCBALR3 SMCR6 1MB (x16)

**Table 2. Memory Selection Assignment** 

#### JTAG security module

The VF48x device includes a JTAG security module to provide maximum security to the memory contents. The visible unlock code can be in the OTP sector or in the first bank of the user-programmable memory. For the VF48x, the visible unlock code is in the OTP sector at address 0x0000\_01F8.

#### memory security module

The VF48x device also includes a memory security module (MSM) to provide additional security and flexibility to the memory contents' protection. The password for unlocking the MSM is located in the four words just before the flash protection keys (see page 17).

#### RAM

The VF48C device contains 64K-bytes of internal static RAM configurable by the SYS module to be addressed within the range of 0x0000\_0000 to 0xFFE0\_0000. This VF48C RAM is implemented in one 64K array selected by two memory-select signals. This VF48C configuration imposes an additional constraint on the memory map for RAM; the starting addresses for both RAM memory selects *cannot* be offset from each other by the multiples of the size of the physical RAM (i.e., 64K for the VF48C device). The VF48C RAM is addressed through memory selects 2 and 3.

The VF48B device contains 48Kbytes of internal static RAM configurable by the SYS module to be addressed within the range of 0x0000\_0000 to 0xFFE0\_0000. This VF48B RAM is implemented in one 48K array selected by two memory-select signals. The VF48B configuration imposes an additional constraint on the memory map



<sup>1</sup> x8 refers to size of memory in 8-bits; x16 refers to size of memory in 16-bits.

<sup>2</sup> The starting addresses for both RAM memory-select signals *cannot* be offset from each other by a multiple of the user-defined block size in the memory-base address register.

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for RAM; the starting addresses for both RAM memory selects *cannot* be offset from each other by the multiples of the size of the physical RAM (i.e., 48K for the VF48B device). The VF48B RAM is addressed through memory selects 2 and 3.

#### **RAM** (continued)

The RAM can be protected by the memory protection unit (MPU) portion of the SYS module, allowing the user finer blocks of memory protection than is allowed by the memory selects. The MPU is ideal for protecting an operating system while allowing access to the current task. For more detailed information on the MPU portion of the SYS module and memory protection, see the memory section of the *TMS470R1x System Module Reference Guide* (literature number SPNU189).

#### F05 flash

The F05 flash memory is a nonvolatile electrically erasable and programmable memory implemented with a 32-bit-wide data bus interface. The F05 flash has an external state machine for programming and erase functions. See the *flash read* and *flash program and erase* sections following.

#### flash protection keys

The VF48x device provides flash protection keys. These four 32-bit protection keys prevent program/erase/compaction operations from occurring until after the four protection keys have been matched by the CPU loading the correct user keys into the FMPKEY control register. The protection keys on the VF48x are located in the last 4 words of the first 64K sector. For more detailed information on the flashflash protection keys and the FMPKEY control register, see the "Optional Quadruple Protection Keys" and "Programming the Protection Keys" portions of the *TMS470R1x F05 Flash Reference Guide* (literature number SPNU213).

#### flash read

The VF48x flash memory is configurable by the SYS module to be addressed within the range of 0x0000\_0000 to 0xFFE0\_0000. The flash is addressed through memory selects 0 and 1.

#### **NOTE**

The flash external pump voltage ( $V_{CCP}$ ) is required for all operations (program, erase, and read).

## flash pipeline mode

When in pipeline mode, the flash operates with a system clock frequency of up to 60 MHz (versus a system clock frequency of 24 MHz in normal mode). Flash in pipeline mode is capable of accessing 64-bit words and provides two 32-bit pipelined words to the CPU. Also, in pipeline mode the flash can be read with no wait states when memory addresses are contiguous (after the initial 1- or 2-wait-state reads).

#### NOTE

After a system reset, pipeline mode is disabled (ENPIPE bit [FMREGOPT.0] is a 0). In other words, the VF48x device powers up and comes out of reset in non-pipeline mode. Furthermore, setting the flash configuration mode bit (GBLCTRL.4) will override pipeline mode.



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### flash program and erase

The VF48C device flash contains two 512K-byte memory arrays (or banks), for a total of 1M-byte of flash, and consists of sixteen sectors. These sixteen sectors are sized as follows:

SECTOR NO.	SEGMENT	LOW ADDRESS	HIGH ADDRESS	MEMORY ARRAYS (OR BANKS)
OTP	2K Bytes	0x0000_0000	0x0000_07FF	
0	64K Bytes	0x0000_0000	0x0000_FFFF	
1	64K Bytes	0x0001_0000	0x0001_FFFF	
2	64K Bytes	0x0002_0000	0x0002_FFFF	DANUG
3	64K Bytes	0x0003_0000	0x0003_FFFF	BANK0 (512K Bytes)
4	64K Bytes	0x0004_0000	0x0004_FFFF	(O12IC Dytes)
5	64K Bytes	0x0005_0000	0x0005_FFFF	
6	64K Bytes	0x0006_0000	0x0006_FFFF	
7	64K Bytes	0x0007_0000	0x0007_FFFF	
0	64K Bytes	0x0008_0000	0x0008_FFFF	
1	64K Bytes	0x0009_0000	0x0009_FFFF	
2	64K Bytes	0x000A_0000	0x000A_FFFF	
3	64K Bytes	0x000B_0000	0x000B_FFFF	BANK1
4	64K Bytes	0x000C_0000	0x000C_FFFF	(512K Bytes)
5	64K Bytes	0x000D_0000	0x000D_FFFF	
6	64K Bytes	0x000E_0000	0x000E_FFFF	
7	64K Bytes	0x000F_0000	0x000F_FFFF	

The VF48B device flash contains one 512K-byte memory array (or bank) and one 256K-byte bank, for a total of 768K-byte of flash, and consists of twelve sectors. These twelve sectors are sized as follows:

SECTOR NO.	SEGMENT	LOW ADDRESS	HIGH ADDRESS	MEMORY ARRAYS (OR BANKS)
OTP	2K Bytes	0x0000_0000	0x0000_007FF	
0	64K Bytes	0x0000_0000	0x0000_FFFF	
1	64K Bytes	0x0001_0000	0x0001_FFFF	
2	64K Bytes	0x0002_0000	0x0002_FFFF	BANKO
3	64K Bytes	0x0003_0000	0x0003_FFFF	BANK0 (512K Bytes)
4	64K Bytes	0x0004_0000	0x0004_FFFF	(OTZIV Dytes)
5	64K Bytes	0x0005_0000	0x0005_FFFF	
6	64K Bytes	0x0006_0000	0x0006_FFFF	
7	64K Bytes	0x0007_0000	0x0007_FFFF	
0	64K Bytes	0x0008_0000	0x0008_FFFF	
1	64K Bytes	0x0009_0000	0x0009_FFFF	BANK1
2	64K Bytes	0x000A_0000	0x000A_FFFF	(256K Bytes)
3	64K Bytes	0x000B_0000	0x000B_FFFF	

The minimum size for an erase operation is one sector. The maximum size for a program operation is one 16-bit word.



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flash program and erase (continued)

#### NOTE

The flash external pump voltage (V<sub>CCP</sub>) is required for all operations (program, erase, and read).

Execution can occur from one bank while programming/erasing any or all sectors of another bank. However, execution cannot occur from any sector within a bank that is being programmed or erased.

#### NOTE

When the OTP sector is enabled, the rest of Flash memory is disabled. The OTP memory can only be read or programmed from code executed out of RAM.

For more detailed information on flash program and erase operations, see the *TMS470R1x F05 Flash Reference Guide* (literature number SPNU213).

### **HET RAM**

The VF48x device contains HET RAM. The HET RAM has a 64-instruction capability. The HET RAM is configurable by the SYS module to be addressed within the range of 0x0000\_0000 to 0xFFE0\_0000. The HET RAM is addressed through memory select 4.



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## peripheral selects and base addresses

The VF48x device uses ten of the sixteen peripheral selects to decode the base addresses of the peripherals. These peripheral selects are fixed and transparent to the user since they are part of the decoding scheme used by the SYS module.

Control registers for the peripherals, SYS module, and flash begin at the base addresses shown in Table 3.

Table 3. VF48x Peripherals, System Module, and Flash Base Addresses

CONNECTING MODILIE	ADDRE	SS RANGE	PERIPHERAL SELECTS	
CONNECTING MODULE	BASE ADDRESS	ENDING ADDRESS	PERIPHERAL SELECTS	
SYSTEM	0xFFFF_FFCC	0xFFFF_FFFF	N/A	
RESERVED	0xFFFF_FF70	0xFFFF_FFCB	N/A	
DWD	0xFFFF_FF60	0xFFFF_FF6F	N/A	
PSA	0xFFFF_FF40	0xFFFF_FF5F	N/A	
CIM	0xFFFF_FF20	0xFFFF_FF3F	N/A	
RTI	0xFFFF_FF00	0xFFFF_FF1F	N/A	
DMA	0xFFFF_FE80	0xFFFF_FEFF	N/A	
DEC	0xFFFF_FE00	0xFFFF_FE7F	N/A	
RESERVED	0xFFFF_FD80	0xFFFF_FDFF	N/A	
MMC	0xFFFF_FD00	0xFFFF_FD7F	N/A	
IEM	0xFFFF_FC00	0xFFFF_FCFF	N/A	
RESERVED	0xFFFF_FB00	0xFFFF_FBFF	N/A	
RESERVED	0xFFFF_FA00	0xFFFF_FAFF	N/A	
DMA CMD BUFFER	0xFFFF_F800	0xFFFF_F9FF	N/A	
MSM	0xFFFF_F700	0xFFFF_F7FF	N/A	
RESERVED	0xFFF8_0000	0xFFFF_F6FF	N/A	
RESERVED	0xFFF7_FD00	0xFFF7_FFFF	DOIO	
HET	0xFFF7_FC00	0xFFF7_FCFF	PS[0]	
RESERVED	0xFFF7_F900	0xFFF7_FBFF	D0(4)	
SPI1	0xFFF7_F800	0xFFF7_F8FF	PS[1]	
RESERVED	0xFFF7_F700	0xFFF7_F7FF		
SCI3	0xFFF7_F600	0xFFF7_F6FF	DOIO	
SCI2	0XFFF7_F500	0XFFF7_F5FF	PS[2]	
SCI1	0xFFF7_F400	0xFFF7_F4FF		
RESERVED	0xFFF7_F100	0xFFF7_F3FF	DOIGI	
MibADC	0xFFF7_F000	0xFFF7_F0FF	PS[3]	
ECP	0xFFF7_EF00	0xFFF7_EFFF		
RESERVED	0xFFF7_EE00	0xFFF7_EEFF	DC(4)	
EBM	0xFFF7_ED00	0xFFF7_EDFF	PS[4]	
GIO	0xFFF7_EC00	0xFFF7_ECFF		



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Table 3. VF48x Peripherals, System Module, and Flash Base Addresses (Continued)

CONNECTING MODULE	ADDRE	SS RANGE	PERIPHERAL SELECTS	
CONNECTING MODULE	BASE ADDRESS	ENDING ADDRESS	PERIPHERAL SELECTS	
HECC2	0xFFF7_EB00	0xFFF7_EBFF		
HECC2	0xFFF7_EA00	0xFFF7_EAFF	PS[5]	
HECC1	0xFFF7_E900	0xFFF7_E9FF	FS[5]	
HECCI	0xFFF7_E800	0xFFF7_E8FF	]	
HECC2 RAM	0xFFF7_E700	0xFFF7_E7FF		
TIECCZ KAWI	0xFFF7_E600	0xFFF7_E6FF	PS[6]	
HECC1 RAM	0xFFF7_E500	0xFFF7_E5FF	٢٥[٥]	
HECCI RAW	0xFFF7_E400	0xFFF7_E4FF		
RESERVED	0xFFF7_E100	0xFFF7_E3FF	PS[7]	
SCC	0xFFF7_E000	0xFFF7_E0FF	F5[/]	
RESERVED	0xFFF7_DD00	0xFFF7_DFFF	PS[8]	
SCC RAM	0xFFF7_DC00	0xFFF7_DCFF	۲۶[٥]	
I2C4	0xFFF7_DB00	0xFFF7_DBFF		
I2C3	0xFFF7_DA00	0xFFF7_DAFF	PS[9]	
12C2	0xFFF7_D900	0xFFF7_D9FF	FS[8]	
I2C1	0xFFF7_D800	0xFFF7_D8FF	]	
RESERVED	0xFFF7_D600	0xFFF7_D7FF		
I2C5	0xFFF7_D500	0xFFF7_D5FF	PS[10]	
SPI2	0xFFF7_D400	0xFFF7_D4FF		
RESERVED	0xFFF7_CC00	0xFFF7_D3FF	PS[11] - PS[12]	
RESERVED	0xFFF7_C800	0xFFF7_CBFF	PS[13]	
RESERVED	0xFFF7_C000	0xFFF7_C7FF	PS[14] - PS[15]	
RESERVED	0xFFF0_0000	0xFFF7_BFFF	N/A	
Flash Control Registers	0xFFE8_8000	0xFFE8_BFFF	N/A	
RESERVED	0xFFF8_4024	0xFFF8_7FFF	N/A	
MPU CONTROL REGISTERS	0xFFE8_4000	0xFFE8_4023	N/A	
RESERVED	0xFFF8_0000	0xFFF8_3FFF	N/A	

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## direct-memory access (DMA)

The direct-memory access (DMA) controller transfers data to and from any specified location in the VF48x memory map (except for restricted memory locations like the system control registers area). The DMA manages up to 16 channels, and supports data transfer for both on-chip and off-chip memories and peripherals. The DMA controller is connected to both the CPU and peripheral buses, enabling these data transfers to occur in parallel with CPU activity and thus maximizing overall system performance.

Although the DMA controller has two possible configurations, for the VF48x device, the DMA controller configuration is 32 control packets and 16 channels.

For the VF48x DMA request hardwired configuration, see Table 4.

Table 4. DMA Request Lines Connections<sup>(1)</sup>

MODULES	DMA REQUEST IN	ITERRUPT SOURCES	DMA CHANNEL
EBM	Expansion Bus DMA request	EBDMAREQ[0]	DMAREQ[0]
SPI1/I2C4	SPI1 end-receive/I2C4 read	SPI1DMA0/I2C4DMA0	DMAREQ[1]
SPI1/I2C4	SPI1 end-transmit/I2C4 write	SPI1DMA1/I2C4DMA1	DMAREQ[2]
MibADC/I2C1	ADC EV/I2C1 read	MibADCDMA0/I2C1DMA0	DMAREQ[3]
MibADC/SCI1/I2C5	ADC G1/SCI1 end-receive/I2C5 read	MibADCDMA1/SCI1DMA0/I2C5DMA0	DMAREQ[4]
MibADC/SCI1/I2C5	ADC G2/SCI1 end-transmit/I2C5 write	MibADCDMA2/SCI1DMA1/I2C5DMA1	DMAREQ[5]
I2C1	I2C1 write	I2C1DMA1	DMAREQ[6]
SCI3/SPI2	SCI3 end-receive/SPI2 end-receive	SCI3DMA0/SPI2DMA0	DMAREQ[7]
SCI3/SPI2	SCI3 end-transmit/SPI2 end- transmit	SCI3DMA01SPI2DMA1	DMAREQ[8]
I2C2	I2C2 read end-receive	I2C2DMA0	DMAREQ[9]
12C2	I2C2 write end-transmit	I2C2DMA1	DMAREQ[10]
12C3	I2C3 read	I2C3DMA0	DMAREQ[11]
I2C3	I2C3 write	I2C3DMA1	DMAREQ[12]
RESERVED			DMAREQ[13]
SCI2	SCI2 end-receive	SCI2DMA0	DMAREQ[14]
SCI2	SCI2 end-transmit	SCI2DMA1	DMAREQ[15]

<sup>1</sup> For DMA channels with more than one assigned request source, *only one* of the sources listed can be the DMA request generator in a given application. The device has software control to ensure that there are no conflicts between requesting modules.

Each channel has two control packets attached to it, allowing the DMA to continuously load RAM and generate periodic interrupts so that the data can be read by the CPU. The control packets allow for the interrupt enable, and the channels determine the priority level of the interrupt.

DMA transfers occur in one of two modes:

- Non-request mode (used when transferring from memory to memory)
- Request mode (used when transferring from memory to peripheral)

For more detailed functional information on the DMA controller, see the *TMS470R1x Direct Memory Access* (DMA) Controller Reference Guide (literature number SPNU194).



## interrupt priority (IEM to CIM)

Interrupt requests originating from the VF48x peripheral modules (i.e., SPI1 or SPI2; SCI1 or SCI2; RTI; etc.) are assigned to channels within the 48-channel interrupt expansion module (IEM) where, via programmable register mapping, these channels are then mapped to the 32-channel central interrupt manager (CIM) portion of the SYS module.

Programming multiple interrupt sources in the IEM to the same CIM channel effectively shares the CIM channel between sources.

The CIM request channels are maskable so that individual channels can be selectively disabled. All interrupt requests can be programmed in the CIM to be of either type:

- Fast interrupt request (FIQ)
- Normal interrupt request (IRQ)

The CIM prioritizes interrupts. The precedences of request channels decrease with ascending channel order in the CIM (0 [highest] and 31 [lowest] priority). For IEM-to-CIM default mapping, channel priorities, and their associated modules, see Table 5.

**Table 5. Interrupt Priority (IEM and CIM)** 

MODULES	INTERRUPT SOURCES	DEFAULT CIM INTERRUPT LEVEL/ CHANNEL	IEM CHANNEL
SPI1	SPI1 end-transfer/overrun	0	0
RTI	COMP2 interrupt	1	1
RTI	COMP1 interrupt	2	2
RTI	TAP interrupt	3	3
SPI2	SPI2 end-transfer/overrun	4	4
GIO	GIO interrupt A	5	5
RESERVED		6	6
HET	HET interrupt 1	7	7
I2C1	I2C1 interrupt	8	8
SCI1/SCI2	SCI1 or SCI2 error interrupt	9	9
SCI1	SCI1 receive interrupt	10	10
RESERVED		11	11
I2C2	I2C2 interrupt	12	12
HECC1	HECC1 interrupt A	13	13
SCC	SCC interrupt A	14	14
RESERVED		15	15
MibADC	MibADC end event conversion	16	16
SCI2	SCI2 receive interrupt	17	17
DMA	DMA interrupt 0	18	18
I2C3	I2C3 interrupt	19	19
SCI1	SCI1 transmit interrupt	20	20
System	SW interrupt (SSI)	21	21
RESERVED		22	22
HET	HET interrupt 2	23	23
HECC1	HECC1 interrupt B	24	24
SCC	SCC interrupt B	25	25



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## interrupt priority (IEM to CIM) (continued)

Table 5. Interrupt Priority (IEM and CIM) (Continued)

MODULES	INTERRUPT SOURCES	DEFAULT CIM INTERRUPT LEVEL/ CHANNEL	IEM CHANNEL
SCI2	SCI2 transmit interrupt	26	26
MibADC	MibADC end Group 1 conversion	27	27
DMA	DMA Interrupt 1	28	28
GIO	GIO interrupt B	29	29
MibADC	MibADC end Group 2 conversion	30	30
SCI3	SCI3 error interrupt	31	31
RESERVED		31	32-37
HECC2	HECC2 interrupt A	31	38
HECC2	HECC2 interrupt B	31	39
SCI3	SCI3 receive interrupt	31	40
SCI3	SCI3 transmit interrupt	31	41
I2C4	I2C4 interrupt	31	42
I2C5	I2C5 interrupt	31	43
RESERVED		31	44-47

For more detailed functional information on the IEM, see the *TMS470R1x Interrupt Expansion Module (IEM)* Reference Guide (literature number SPNU211). For more detailed functional information on the CIM, see the *TMS470R1x System Module Reference Guide* (literature number SPNU189).



## expansion bus module (EBM)

The expansion bus module (EBM) is a standalone module used to bond out both general-purpose input/output pins and expansion bus interface pins. This module supports the multiplexing of the GIO functions and the expansion bus interface functions. The module also supports 8- and 16- bit expansion bus memory interface mappings as well as mapping of the following expansion bus signals:

- 27-bit address bus (EBADDR[26:0]) for x8, 19-bit address bus (EBADDR[18:0]) for x16
- 8- or 16-bit data bus (EBDATA[7:0] or EBDATA[15:0])
- 2 write strobes (EBWR[1:0])
- 2 memory chip selects (EBCS[6:5])
- 1 output enable (EBOE)
- 1 external hold signal for interfacing to slow memories (EBHOLD)
- 1 DMA request line (EBDMAREQ[0])

Table 6 shows the multiplexing (muxing) of I/O signals with the expansion bus interface signals. The mapping of these pins varies depending on the memory mode.

Table 6. Expansion Bus Mux Mapping<sup>(1)</sup>

GIO	EXPANSION BUS	MODULE PINS <sup>(2)</sup>
GIO	X8	X16
GIOB[0]	EBDMAREQ[0]	EBDMAREQ[0]
GIOC[0]	EBOE	EBOE
GIOC[2:1]	EBWR[1:0]	EBWR[1:0]
GIOC[4:3]	EBCS[6:5]	EBCS[6:5]
GIOD[5:0]	EBADDR[5:0]	EBADDR[5:0]
GIOE[7:0]	EBDATA[7:0]	EBDATA[7:0]
GIOF[7:0]	EBADDR[13:6]	EBDATA[15:8]
GIOG[7:0]	EBADDR[21:14]	EBADDR[13:6]
GIOH[5]	EBHOLD	EBHOLD
I2C5SDA	EBADDR[26]	EBADDR[18]
I2C5SCL	EBADDR[25]	EBADDR[17]
I2C4SCL	EBADDR[24]	EBADDR[16]
I2C4SDA	EBADDR[23]	EBADDR[15]
GIOH[0]	EBADDR[22]	EBADDR[14]

<sup>1</sup> These mappings are controlled by the EBM mux control registers B–H (EBMXCRB–EBMXCRH) and the EBM control register 1 (EBMCR1). For more detailed information, see the TMS470R1x Expansion Bus Module (EBM) Reference Guide (literature number SPNU222) and the TMS470R1x General Purpose Input/Output Reference Guide (literature number SPNU192).

Table 7 lists the names of the expansion bus interface signals and their functions.

Table 7. Expansion Bus Pins

PIN	DESCRIPTION
EBDMAREQ	Expansion bus DMA request
EBOE	Expansion bus pin enable
EBWR	Expansion bus write strobe. EBWR[1] controls EBDATA[15:8] and EBWR[0] controls EBDATA[7:0]
EBCS	Expansion bus chip select
EBADDR	Expansion bus address pin
EBDATA	Expansion bus data pin
EBHOLD	Expansion bus hold. An external device may assert this signal to add wait states to an expansion bus transaction.



<sup>2</sup> X8 refers to size of memory in 8-bits; X16 refers to size of memory in 16-bits.

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#### **MibADC**

The multi-buffered analog-to-digital converter (MibADC) accepts an analog signal and converts the signal to a 10-bit digital value.

The VF48x MibADC module can function in two modes: compatibility mode, where its programmer's model is compatible with the TMS470R1x ADC module and its digital results are stored in digital result registers; or in buffered mode, where the digital result registers are replaced with three FIFO buffers, one for each conversion group [event, group1 (G1), and group2 (G2)]. In buffered mode, the MibADC buffers can be serviced by interrupts or by the DMA.

## MibADC event trigger enhancements

The MibADC includes two major enhancements over the event-triggering capability of the TMS470R1x ADC.

- Both group 1 and the event group can be configured for event-triggered operation, providing up to two
  event-triggered groups.
- The trigger source and polarity can be selected individually for both group 1 and the event group from the options identified in Table 8.

EVENT#	SOURCE SELECT BITS FOR G1 OR EVENT (G1SRC[1:0] or EVSRC[1:0])	SIGNAL PIN NAME
EVENT1	00	ADEVT
EVENT2	01	HET18
EVENT3	10	RESERVED
EVENT4	11	RESERVED

**Table 8. MibADC Event Hookup Configuration** 

For group 1, these event-triggered selections are configured via the group 1 source select bits (G1SRC[1:0]) in the AD event source register (ADEVTSRC.[5:4]). For the event group, these event-triggered selections are configured via the event group source select bits (EVSRC[1:0]) in the AD event source register (ADEVTSRC.[1:0]).

For more detailed functional information on the MibADC, see the *TMS470R1x Multi-Buffered Analog-to-Digital Converter (MibADC) Reference Guide* (literature number SPNU206).



## JTAG interface

There are two main test access ports (TAPs) on the VF748C device:

- TMS470R1x CPU TAP
- Device TAP for factory test

Some of the JTAG pins are shared among these two TAPs. The hookup is illustrated in Figure 3.

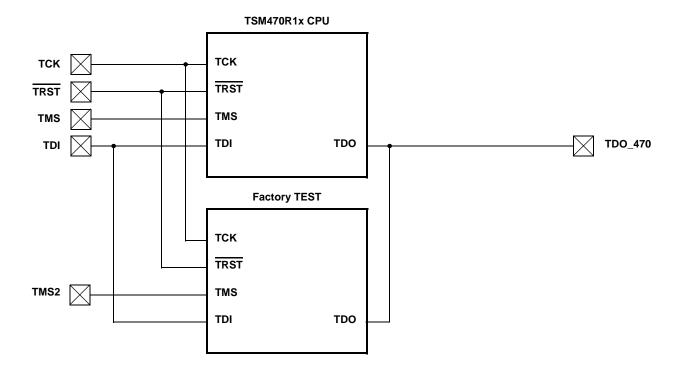


Figure 3. JTAG Interface

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### development system support

Texas Instruments provides extensive hardware and software development support tools for the TMS470R1x family. These support tools include:

- Code Composer Studio™ Integrated Development Environment (IDE)
  - Fully integrated suite of software development tools
  - Includes Compiler/Assembler/Linker, Debugger, and Simulator
  - Supports Real-Time analysis, data visualization, and open API
- Optimizing C compiler
  - Supports high-level language programming
  - Full implementation of the standard ANSI C language
  - Powerful optimizer that improves code-execution speed and reduces code size
  - Extensive run-time support library included
  - TMS470R1x control registers easily accessible from the C program
  - Interfaces C functions and assembly functions easily
  - Establishes comprehensive, easy-to-use tool set for the development of high-performance microcontroller applications in C/C++
- Assembly language tools (assembler and linker)
  - Provides extensive macro capability
  - Allows high-speed operation
  - Allows extensive control of the assembly process using assembler directives
  - Automatically resolves memory references as C and assembly modules are combined
- TMS470R1x CPU Simulator
  - Provides capability to simulate CPU operation without emulation hardware
  - Allows inspection and modifications of memory locations
  - Allows debugging programs in C or assembly language
- XDS emulation communication kits
  - Allows high-speed JTAG communication to the TMS470R1x emulator or target board

For more information on pricing and availability, contact the nearest TI field sales office or authorized distributor.

Code Composer Studio is a trademark of Texas Instruments.



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#### documentation support

Extensive documentation supports all of the TMS470 microcontroller family generation of devices. The types of documentation available include: data sheets with design specifications; complete user's guides for all devices and development support tools; and hardware and software applications. Useful reference documentation includes:

#### User's Guides

- TMS470R1x 32-Bit RISC Microcontroller Family User's Guide (literature number SPNU134)
- TMS470R1x C/C++ Compiler User's Guide (literature number SPNU151)
- TMS470R1x Code Generation Tools Getting Started Guide (literature number SPNU117)
- TMS470R1x C Source Debugger User's Guide (literature number SPNU124)
- TMS470R1x Assembly Language Tools User's Guide (literature number SPNU118)
- TMS470R1x System Module Reference Guide (literature number SPNU189)
- TMS470R1x Direct Memory Access (DMA) Controller Reference Guide (literature number SPNU194)
- TMS470R1x Serial Peripheral Interface (SPI) Reference Guide (literature number SPNU195)
- TMS470R1x Serial Communication Interface (SCI) Reference Guide (literature number SPNU196)
- TMS470R1x Controller Area Network (CAN) Reference Guide (literature number SPNU197)
- TMS470R1x High-End Timer (HET) Reference Guide (literature number SPNU199)
- TMS470R1x External Clock Prescale (ECP) Reference Guide (literature number SPNU202)
- TMS470R1x Multi-Buffered Analog-to-Digital Converter (MibADC) Reference Guide (literature number SPNU206)
- TMS470R1x F05 Flash Reference Guide (literature number SPNU213)
- TMS470R1x Frequency-Modulated Phase-Locked Loop (FMPLL) Clock Module Reference Guide (literature number SPNU221)
- TMS470R1x Expansion Bus Module (EBM) Reference Guide (literature number SPNU222)
- TMS470R1x Inter-Integrated Circuit (I2C) Reference Guide (literature number SPNU223)
- TMS470R1x JTAG Security Module Reference Guide (literature number SPNU245)
- TMS470R1x Memory Security Module Reference Guide (literature number SPNU246)

### Application Reports:

- Analog Watchdog Resistor, Capacitor and Discharge Interval Selection Constraints (literature number SPNA005)
- F05/C05 Power Up Reset and Power Sequencing Requirements (literature number SPNA009)



## device numbering conventions

Figure 4 illustrates the numbering and symbol nomenclature for the TMS470R1x family.

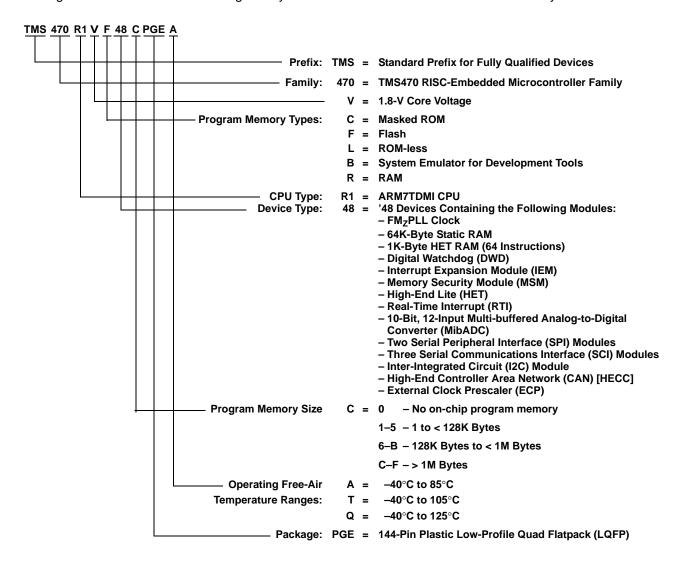


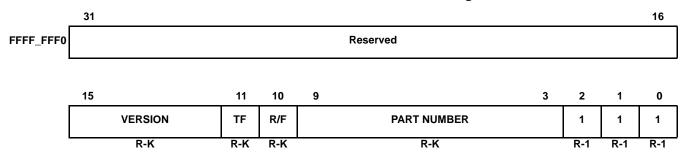
Figure 4. TMS470R1x Family Nomenclature



## device identification code register

The device identification code register identifies the silicon version, the technology family (TF), a ROM or flash device, and an assigned device-specific part number (see Table 9). The VF48x device identification code register value is 0x0A5F.

Table 9. TMS470 Device ID Bit Allocation Register



LEGEND:

For bits 3–15: R = Read only, -K = Value constant after RESET

For bits 0–2: R = Read only, -1 = Value after RESET

## Transmission Request Reset Register (CANTRR) Field Descriptions

Bit	Name	Value	Description
31–16	Reserved		Reads are undefined and writes have no effect.
15–12	VERSION		Silicon version (revision) bits These bits identify the silicon version of the device.
11	TF		Technology family bit This bit distinguishes the technology family core power supply:
		0	3.3 V for F10/C10 devices
		1	1.8 V for F05/C05 devices
10	R/F		ROM/flash bit This bit distinguishes between ROM and flash devices:
		0	Flash device
		1	ROM device
9–3	PART NUM- BER		Device-specific part number bits These bits identify the assigned device-specific part number. The assigned device-specific part number for the VF48x device is 1001011.
2–0	1 Mandatory High		Bits 2, 1, and 0 are tied high by default.

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## device part numbers

Table 10 lists all the available TMS470R1VF48x devices.

**Table 10. Device Part Numbers** 

DEVICE PART NUMBER	PROGRAM MEMORY		PACKAGE TYPE	TEMPERATURE RANGES			
	ROM	FLASH EEPROM	144-PIN LQFP	–40°C TO 85°C	-40°C TO 105°C	–40°C TO 125°C	
TMS470R1VF48BPGEA		Х	Х	Х			
TMS470R1VF48BPGET		Х	X		Х		
TMS470R1VF48BPGEQ		Х	X			X	
TMS470R1VF48CPGEA		Х	Х	Х			
TMS470R1VF48CPGET		Х	X		Х		
TMS470R1VF48CPGEQ		Х	X			X	

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#### **DEVICE ELECTRICAL SPECIFICATIONS AND TIMING PARAMETERS**

# absolute maximum ratings over operating free-air temperature range, A version (unless otherwise noted)<sup>(1)</sup>

Supply voltage ranges: V <sub>CC</sub> <sup>(2)</sup>	0.3 V to 2.5 V
Supply voltage ranges: V <sub>CCIO</sub> , V <sub>CCAD</sub> , V <sub>CCP</sub> (flash pump) <sup>(2)</sup>	0.3 V to 4.1 V
Input voltage range: All 5 V tolerant input pins	0.3 V to 6.0 V
All other input pins	0.3 V to 4.1 V
Input clamp current: All 5 V tolerant pins, $\overline{PORRST}$ , $\overline{TRST}$ , TEST and TCK (V <sub>I</sub> < 0)	–20mA
ADIN[0:11] $I_{IK}$ ( $V_I < 0$ or $V_I > V_{CCAD}$ )	±10 mA
All other pins $I_{IK}$ ( $V_I < 0$ or $V_I > V_{CCIO}$ )	±20 mA
Operating free-air temperature ranges, T <sub>A</sub> : A version	40°C to 85°C
T version	40°C to 105°C
Q version	40°C to 125°C
Operating junction temperature range, T <sub>J</sub>	40°C to 150°C
Storage temperature range, T <sub>stg</sub>	40°C to 150°C

<sup>1</sup> Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

## device recommended operating conditions(3)

			MIN	NOM	MAX	UNIT
V	Digital lagis supply valtage (Care)	SYSCLK = 48MHz (pipeline mode enabled)	1.71		2.05	
$V_{CC}$	Digital logic supply voltage (Core)	SYSCLK = 60MHz (pipeline mode enabled)	1.81		2.05	V
V <sub>CCIO</sub>	Digital logic supply voltage (I/O)		3		3.6	V
$V_{CCAD}$	ADC supply voltage		3		3.6	V
$V_{CCP}$	Flash pump supply voltage		3		3.6	V
V <sub>SS</sub>	Digital logic supply ground			0		V
V <sub>SSAD</sub>	ADC supply ground <sup>(3)</sup>		- 0.1		0.1	V
		A version	- 40		85	°C
$T_A$	Operating free-air temperature	T version	- 40		105	
		Q version	- 40		125	°C
TJ	Operating junction temperature		- 40		150	°C

<sup>3</sup> All voltages are with respect to  $V_{SS}$ , except  $V_{CCAD}$ , which is with respect to  $V_{SSAD}$ .



<sup>2</sup> All voltage values are with respect to their associated grounds.

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# electrical characteristics over recommended operating free-air temperature range, A version (unless otherwise noted)<sup>(1)</sup>

PARAMETER			TEST CONDITIONS	MIN	TYP	MAX	UNIT
$V_{hys}$	Input hysteresis			0.15			V
$V_{IL}$	Low-level input voltage	All inputs <sup>(2)</sup>		- 0.3		0.8	V
$V_{IH}$	High-level input voltage	All inputs		2		V <sub>CCIO</sub> +0.3	V
$V_{th}$	Input threshold voltage	AWD only <sup>(3)</sup>		1.35		1.8	V
\/			$I_{OL} = I_{OL} MAX$			0.2 V <sub>CCIO</sub>	V
$V_{OL}$	Low-level output voltage <sup>(4)</sup>		I <sub>OL</sub> = 50 μA			0.2	V
\/			I <sub>OH</sub> = I <sub>OH</sub> MIN	0.8 V <sub>CCIO</sub>			V
V <sub>OH</sub>	High-level output voltage(4)	High-level output voltage <sup>(4)</sup>		V <sub>CCIO</sub> - 0.2			\ \
I <sub>IC</sub>	Input clamp current (I/O pins)(5	5)	$V_1 < V_{SSIO} - 0.3 \text{ or } V_1 > V_{CCIO} + 0.3$	-2		2	mA
		I <sub>IL</sub> Pulldown	$V_I = V_{SS}$	-1		1	
		I <sub>IH</sub> Pulldown	V <sub>I</sub> = V <sub>CCIO</sub>	5		40	
	Input current (3.3 V input pins)	I <sub>IL</sub> Pullup	$V_I = V_{SS}$	-40		-5	μА
		I <sub>IH</sub> Pullup	$V_I = V_{CCIO}$	-1		1	
I <sub>I</sub>		All other pins	No pullup or pulldown	-1		1	1
			$V_I = V_{SS}$	-1		1	
	Innut ourrent (F. \/ telerent innu	t nina)	$V_I = V_{CCIO}$	1		5	_
	Input current (5 V tolerant input	it pins)	V <sub>I</sub> = 5 V	5		25	μΑ
			V <sub>I</sub> = 5.5 V	25		50	1
	Low-level output	CLKOUT, AWD, TDI, TDO, TMS, TMS2				8	
$I_{OL}$	current	RST	$V_{OL} = V_{OL} MAX$			4	^
		All other 3.3 V I/O <sup>(6)</sup>				2	mA
		5 V tolerant				4	
		CLKOUT, TDI, TDO, TMS, TMS2		-8			
I <sub>OH</sub>	High-level output	RST	$V_{OH} = V_{OH} MIN$	-4			A
	current	All other 3.3 V I/O <sup>(6)</sup>		-2			mA
	5 V tolerant		1	-4			

- 1 Source currents (out of the device) are negative while sink currents (into the device) are positive.
- 2 This does not apply to the PORRST pin. For PORRST exceptions, see the RST and PORRST timings section on page 41.
- 3 These values help to determine the external RC network circuit. For more details, see the *TMS470R1x System Module Reference Guide* (literature number SPNU189).
- 4 V<sub>OL</sub> and V<sub>OH</sub> are linear with respect to the amount of load current (I<sub>OL</sub>/I<sub>OH</sub>) applied.
- 5 Parameter does not apply to input-only or output-only pins.
- 6 Some of the 2 mA buffers on this device are zero-dominant buffers, as indicated by a -z in the Output Current column of the Terminal Functions table. If two of these buffers are shorted together and one is outputting a low level and the other is outputting a high level, the resulting value will always be low.
- 7 The typical values indicated in this table are the expected values during operation under normal operating conditions: nominal  $V_{CC}$ ,  $V_{CCIO}$ , or  $V_{CCAD}$ , room temperature.
- 8 For flash banks/pumps in sleep mode.
- 9 For reduced power consumption in low power mode, CANSRX and CANSTX should be driven output LOW.
- 10 I/O pins configured as inputs or outputs with no load. All pulldown inputs  $\leq$  0.2 V. All pullup inputs  $\geq$  V<sub>CCIO</sub> 0.2 V.



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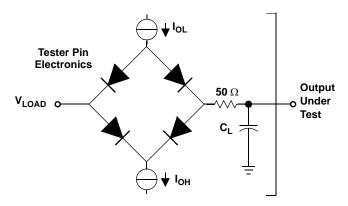
# electrical characteristics over recommended operating free-air temperature range, A version (unless otherwise noted)<sup>(1)</sup> (continued)

PARAMETER		TEST CONDITIONS	MIN	<b>TYP</b> <sup>(7)</sup>	MAX	UNIT
	V <sub>CC</sub> Digital supply current (operating mode)	SYSCLK = 48 MHz, $V_{CC}$ = 2.05 V			125	mA
		SYSCLK = 60 MHz, $V_{CC}$ = 2.05 V			125	mA
I <sub>CC</sub>	V <sub>CC</sub> Digital supply current (standby mode) <sup>(8)(9)</sup>	OSCIN = 5 MHz, $V_{CC}$ = 2.05 V			1.30	mA
	V <sub>CC</sub> Digital supply current (halt mode) <sup>(8)(9)</sup>	V <sub>CC</sub> = 2.05 V			700	μА
	V <sub>CCIO</sub> Digital supply current (operating mode)	No DC load, V <sub>CCIO</sub> = 3.6 V <sup>(10)</sup>			15	mA
I <sub>CCIO</sub>	V <sub>CCIO</sub> Digital supply current (standby mode) <sup>(9)</sup>	No DC load, V <sub>CCIO</sub> = 3.6 V <sup>(10)</sup>			10	μА
	V <sub>CCIO</sub> Digital supply current (halt mode) <sup>(9)</sup>	No DC load, V <sub>CCIO</sub> = 3.6 V <sup>(10)</sup>			10	μА
	V <sub>CCAD</sub> supply current (operating mode)	All frequencies, V <sub>CCAD</sub> = 3.6 V			15	mA
$I_{CCAD}$	V <sub>CCAD</sub> supply current (standby mode)	No DC load, V <sub>CCAD</sub> = 3.6 V			10	μА
	V <sub>CCAD</sub> supply current (halt mode)	V <sub>CCAD</sub> = 3.6 V			10	μА
	V <sub>CCP</sub> pump supply current	SYSCLK = 48 MHz, V <sub>CCP</sub> = 3.6 V read operation			45	mA
I <sub>CCP</sub>		SYSCLK = 60 MHz, V <sub>CCP</sub> = 3.6 V read operation			55	
ICCP		V <sub>CCP</sub> = 3.6 V program and erase			70	mA
		V <sub>CCP</sub> = 3.6 V standby mode operation <sup>(8)</sup>			10	μА
		V <sub>CCP</sub> = 3.6 V halt mode operation <sup>(8)</sup>			10	μА
C <sub>I</sub>	Input capacitance			2		pF
Co	Output capacitance			3		pF

- 1 Source currents (out of the device) are negative while sink currents (into the device) are positive.
- 2 This does not apply to the PORRST pin. For PORRST exceptions, see the RST and PORRST timings section on page 41.
- 3 These values help to determine the external RC network circuit. For more details, see the *TMS470R1x System Module Reference Guide* (literature number SPNU189).
- 4  $V_{OL}$  and  $V_{OH}$  are linear with respect to the amount of load current ( $I_{OL}/I_{OH}$ ) applied.
- 5 Parameter does not apply to input-only or output-only pins.
- 6 Some of the 2 mA buffers on this device are zero-dominant buffers, as indicated by a -z in the Output Current column of the Terminal Functions table. If two of these buffers are shorted together and one is outputting a low level and the other is outputting a high level, the resulting value will always be low.
- 7 The typical values indicated in this table are the expected values during operation under normal operating conditions: nominal V<sub>CC</sub>, V<sub>CCIO</sub>, or V<sub>CCAD</sub>, room temperature.
- 8 For flash banks/pumps in sleep mode.
- 9 For reduced power consumption in low power mode, CANSRX and CANSTX should be driven output LOW.
- 10 I/O pins configured as inputs or outputs with no load. All pulldown inputs  $\leq$  0.2 V. All pullup inputs  $\geq$  V<sub>CCIO</sub> 0.2 V.



## PARAMETER MEASUREMENT INFORMATION



Where:  $I_{OL} = I_{OL}$  MAX for the respective  $pin^{(A)}$ 

 $I_{OH}$ = $I_{OH}$  MIN for the respective pin<sup>(A)</sup>

 $V_{LOAD}$ =1.5 V

C<sub>L</sub>=150-pF typical load-circuit capacitance<sup>(B)</sup>

- A. For these values, see the "electrical characteristics over recommended operating free-air temperature range" table.
- B. All timing parameters measured using an external load capacitance of 150 pF unless otherwise noted.

Figure 5. Test Load Circuit



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#### timing parameter symbology

Timing parameter symbols have been created in accordance with JEDEC Standard 100. To shorten the symbols, some of the pin names and other related terminology have been abbreviated as follows:

CM	Compaction, CMPCT	RD	Read
CO	CLKOUT	RST	Reset, RST
ER	Erase	RX	SCInRX
ICLK	Interface clock	S	Slave mode
M	Master mode	SCC	SCInCLK
OSC, OSCI	OSCIN	SIMO	SPInSIMO
OSCO	OSCOUT	SOMI	SPInSOMI
Р	Program, PROG	SPC	SPInCLK
R	Ready	SYS	System clock
R0	Read margin 0, RDMRGN0	TX	SCInTX
R1	Read margin 1, RDMRGN1		

Lowercase subscripts and their meanings are:

а	access time	r	rise time
С	cycle time (period)	su	setup time
d	delay time	t	transition time
f	fall time	V	valid time

h hold time w pulse duration (width)

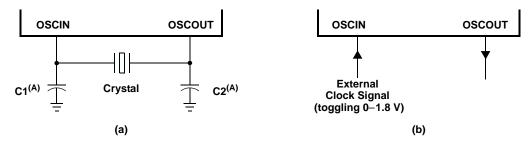
The following additional letters are used with these meanings:

Н	High	X	Unknown, changing, or don't care level
L	Low	Z	High impedance
V	Valid		

#### external reference resonator/crystal oscillator clock option

The oscillator is enabled by connecting the appropriate fundamental 4–10 MHz resonator/crystal and load capacitors across the external OSCIN and OSCOUT pins as shown in Figure 6a. The oscillator is a single-stage inverter held in bias by an integrated bias resistor. This resistor is disabled during leakage test measurement and HALT mode. TI strongly encourages each customer to submit samples of the device to the resonator/crystal vendors for validation. The vendors are equipped to determine what load capacitors will best tune their resonator/crystal to the microcontroller device for optimum start-up and operation over temperature/voltage extremes.

An external oscillator source can be used by connecting a 1.8 V clock signal to the OSCIN pin and leaving the OSCOUT pin unconnected (open) as shown in Figure 6b.



A. The values of C1 and C2 should be provided by the resonator/crystal vendor.

Figure 6. Crystal/Clock Connection



#### FM<sub>7</sub>PLL and clock specifications

#### timing requirements for FM<sub>Z</sub>PLL circuits enabled or disabled

		MIN	TYP	MAX	UNIT
f <sub>(OSC)</sub>	Input clock frequency	4		10	MHz
t <sub>c(OSC)</sub>	Cycle time, OSCIN	100			ns
t <sub>w(OSCIL)</sub>	Pulse duration, OSCIN low	15			ns
t <sub>w(OSCIH)</sub>	Pulse duration, OSCIN high	15			ns
f <sub>(OSCRST)</sub>	OSC FAIL frequency <sup>(1)</sup>		53		kHz

<sup>1</sup> Causes a device reset (specifically a clock reset) by setting the RST OSC FAIL (GLBCTRL.15) and the OSC FAIL flag (GLBSTAT.1) bits equal to 1. For more detailed information on these bits and device resets, see the *TMS470R1x System Module Reference Guide* (literature number SPNU189).

#### switching characteristics over recommended operating conditions for clocks(1)(2)(3)

	PARAMETER	TEST CONDITIONS <sup>(4)</sup>	MIN	MAX	UNIT
franco	Custom sleet from (5)	Pipeline mode enabled		60 <sup>(6)</sup>	MHz
f <sub>(SYS)</sub>	System clock frequency <sup>(5)</sup>	Pipeline mode disabled		24	MHz
f <sub>(CONFIG)</sub>	System clock frequency - flash config mode			24	MHz
f	Interface clock frequency	Pipeline mode enabled		30	MHz
f <sub>(ICLK)</sub>	interface clock frequency	Pipeline mode disabled		24	MHz
f	External clock output frequency for ECD module	Pipeline mode enabled		30	MHz
f(ECLK)	External clock output frequency for ECP module	Pipeline mode disabled		24	MHz
t	Cycle time, system clock	Pipeline mode enabled	16.7		ns
t <sub>c(SYS)</sub>	Cycle time, system clock	Pipeline mode disabled	41.6		ns
t <sub>c(CONFIG)</sub>	Cycle time, system clock - flash config mode		41.6		ns
<b>1</b>	Cycle time interfere cleak	Pipeline mode enabled	33.3		ns
t <sub>c(ICLK)</sub>	Cycle time, interface clock	Pipeline mode disabled	41.6		ns
t	Cycle time ECD module external cleak output	Pipeline mode enabled	33.3		ns
<sup>t</sup> c(ECLK)	Cycle time, ECP module external clock output	Pipeline mode disabled	41.6		ns

<sup>1</sup> f<sub>(SYS)</sub> = M × f<sub>(OSC)</sub> / R, where M = {8}, R = {1,2,3,4,5,6,7,8} when PLLDIS = 0. R is the system-clock divider determined by the CLKDIVPRE [2:0] bits in the global control register (GLBCTRL.[2:0]) and M is the PLL multiplier determined by the MULT4 bit also in the GLBCTRL register (GLBCTRL.3).

- 2  $f_{(ECLK)} = f_{(ICLK)} / N$ , where N = {1 to 256}. N is the ECP prescale value defined by the ECPCTRL.[7:0] register bits in the ECP module.
- 3 Only ZPLL mode is available. FM mode must not be turned on.
- 4 Pipeline mode enabled or disabled is determined by the ENPIPE bit (FMREGOPT.0).
- 5 Flash Vread must be set to 5V to achieve maximum system clock frequency.
- 6 Operating V<sub>CC</sub> range for this system clock frequency is 1.81 to 2.05V.



 $f_{(SYS)} = f_{(OSC)} / R$ , where R = {1,2,3,4,5,6,7,8} when PLLDIS = 1.

 $f_{\text{(ICLK)}} = f_{\text{(SYS)}} / X$ , where  $X = \{1,2,3,4,5,6,7,8,9,10,11,12,13,14,15,16\}$ . X is the interface clock divider ratio determined by the PCR0.[4:1] bits in the SYS module.

#### FM<sub>Z</sub>PLL and clock specifications (continued)

## switching characteristics over recommended operating conditions for external clocks (see Figure 7 and Figure 8)<sup>(1)(2)(3)</sup>

NO.	PARAMETER	TEST CONDITIONS	MIN	MAX	UNIT
		SYSCLK or MCLK <sup>(4)</sup>	$0.5t_{c(SYS)} - t_f$		
1	$t_{w(COL)}$ Pulse duration, CLKOUT low	ICLK: X is even or 1 <sup>(5)</sup> .	$0.5t_{c(ICLK)} - t_{f}$		ns
		ICLK: X is odd and not 1. <sup>(5)</sup>	$0.5t_{c(ICLK)} + 0.5t_{c(SYS)} - t_f$		
		SYSCLK or MCLK <sup>(4)</sup>	$0.5t_{c(SYS)} - t_r$		
2	$t_{w(COH)}$ Pulse duration, CLKOUT high	ICLK: X is even or 1. <sup>(5)</sup>	$0.5t_{c(ICLK)} - t_r$		ns
		ICLK: X is odd and not 1. <sup>(5)</sup>	$0.5t_{\text{c(ICLK)}} - 0.5t_{\text{c(SYS)}} - t_{\text{r}}$		
		N is even and X is even or odd.	$0.5t_{c(ECLK)} - t_{f}$		
3	t <sub>w(EOL)</sub> Pulse duration, ECLK low	N is odd and X is even.	$0.5t_{c(ECLK)} - t_{f}$		ns
		N is odd and X is odd and not 1.	$0.5t_{c(ECLK)} + 0.5t_{c(SYS)} - t_{f}$		
		N is even and X is even or odd.	$0.5t_{c(ECLK)} - t_r$		
4	t <sub>w(EOH)</sub> Pulse duration, ECLK high	N is odd and X is even.	$0.5t_{c(ECLK)} - t_r$		ns
		N is odd and X is odd and not 1.	$0.5t_{c(ECLK)} - 0.5t_{c(SYS)} - t_r$		

- 1  $X = \{1,2,3,4,5,6,7,8,9,10,11,12,13,14,15,16\}$ . X is the interface clock divider ratio determined by the PCR0.[4:1] bits in the SYS module.
- 2 N = {1 to 256}. N is the ECP prescale value defined by the ECPCTRL.[7:0] register bits in the ECP module.
- 3 CLKOUT/ECLK pulse durations (low/high) are a function of the OSCIN pulse durations when PLLDIS is active.
- 4 Clock source bits are selected as either SYSCLK (CLKCNTL.[6:5] = 11 binary) or MCLK (CLKCNTL.[6:5] = 10 binary).
- 5 Clock source bits are selected as ICLK (CLKCNTL.[6:5] = 01 binary).

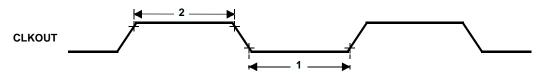


Figure 7. CLKOUT Timing Diagram

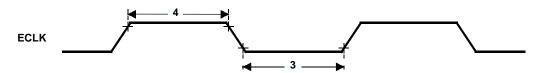


Figure 8. ECLK Timing Diagram

## RST and PORRST timings

## timing requirements for PORRST<sup>(1)</sup> (see Figure 9)

NO.			MIN	MAX	UNIT
	V <sub>CCPORL</sub>	V <sub>CC</sub> low supply level when PORRST must be active during power up		0.6	V
	V <sub>CCPORH</sub>	V <sub>CC</sub> high supply level when PORRST must remain active during power up and become active during power down	1.5		V
	V <sub>CCIOPORL</sub>	V <sub>CCIO</sub> low supply level when PORRST must be active during power up		1.1	V
	V <sub>CCIOPORH</sub>	V <sub>CCIO</sub> high supply level when PORRST must remain active during power up and become active during power down	2.75		V
	V <sub>IL</sub>	Low-level input voltage after V <sub>CCIO</sub> > V <sub>CCIOPORH</sub>		0.2 V <sub>CCIO</sub>	V
	V <sub>IL(PORRST)</sub>	Low-level input voltage of PORRST before V <sub>CCIO</sub> > V <sub>CCIOPORL</sub>		0.5	V
3	t <sub>su(PORRST)r</sub>	Setup time, PORRST active before V <sub>CCIO</sub> > V <sub>CCIOPORL</sub> during power up	0		ms
5	t <sub>su(VCCIO)</sub> r	Setup time, V <sub>CCIO</sub> > V <sub>CCIOPORL</sub> before V <sub>CC</sub> > V <sub>CCPORL</sub>	0		ms
6	t <sub>h(PORRST)r</sub>	Hold time, PORRST active after V <sub>CC</sub> > V <sub>CCPORH</sub>	1		ms
7	t <sub>su(PORRST)f</sub>	Setup time, PORRST active before V <sub>CC</sub> ≤ V <sub>CCPORH</sub> during power down	8		μS
8	t <sub>h(PORRST)rio</sub>	Hold time, PORRST active after V <sub>CCIO</sub> > V <sub>CCIOPORH</sub>	1		ms
9	t <sub>h(PORRST)d</sub>	Hold time, PORRST active after V <sub>CC</sub> < V <sub>CCPORL</sub>	0		ms
10	t <sub>su(PORRST)fio</sub>	Setup time, PORRST active before V <sub>CCIO</sub> ≤ V <sub>CCIOPORH</sub> during power down	0		ns
11	t <sub>su(VCCIO)f</sub>	Setup time, V <sub>CC</sub> < V <sub>CCPORL</sub> before V <sub>CCIO</sub> < V <sub>CCIOPORL</sub>	0	_	ns

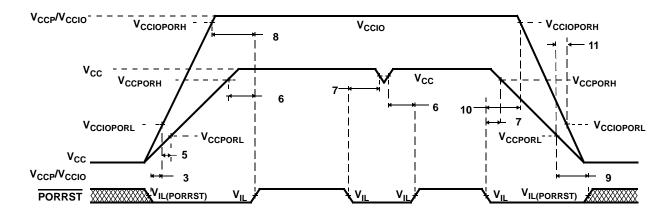


Figure 9. PORRST Timing Diagram

## switching characteristics over recommended operating conditions for $\overline{\text{RST}}^{(1)}$

	PARAMETER	MIN	MAX	UNIT
t	Valid time, RST active after PORRST inactive	4112t <sub>c(OSC)</sub> 8t <sub>c(SYS)</sub>		ne
t <sub>v(RST)</sub>	Valid time, RST active (all others)			ns
t <sub>fsu</sub>	Flash start up time, from RST inactive to fetch of first instruction from flash (flash pump stabilization time)	836t <sub>c(OSC)</sub>		ns

<sup>1</sup> Specified values do NOT include rise/fall times. For rise and fall timings, see the "switching characteristics for output timings versus load capacitance" table.



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## JTAG scan interface timing (JTAG clock specification 10-MHz and 50-pF load on TDO output)

NO.			MIN	MAX	UNIT
1	t <sub>c(JTAG)</sub>	Cycle time, JTAG low and high period	50		ns
2	t <sub>su(TDI/TMS - TCKr)</sub>	Setup time, TDI, TMS before TCK rise (TCKr)	15		ns
3	t <sub>h(TCKr</sub> -TDI/TMS)	Hold time, TDI, TMS after TCKr	15		ns
4	t <sub>h(TCKf</sub> -TDO)	Hold time, TDO after TCKf	10		ns
5	t <sub>d(TCKf</sub> -TDO)	Delay time, TDO valid after TCK fall (TCKf)		45	ns

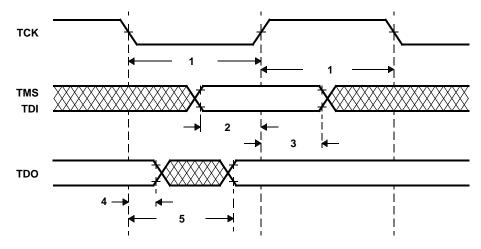


Figure 10. JTAG Scan Timings

## output timings

## switching characteristics for output timings versus load capacitance (C<sub>L</sub>) (see Figure 11)

$\begin{array}{c cccc} C_L = 150 \text{ pF} & 9 & 28 \\ \hline C_L = 400 \text{ pF} & 18 & 40 \\ \hline C_L = 15 \text{ pF} & 2 & 8 \\ \hline C_L = 50 \text{ pF} & 2.5 & 9 \\ \hline \end{array}$		PARAMETER		MIN	MAX	UNIT
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$			C <sub>L</sub> = 15 pF	0.5	2.5	
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$		Disa time ANNID CHICALLY TOLL TOO TAKE TAKES	C <sub>L</sub> = 50 pF	1.5	5.0	
$t_{t_{1}}  \text{Fall time, AWD, CLKOUT, TDI, TDO, TMS, TMS2}  \begin{cases} C_{L} = 15  \text{pF} & 0.5 & 2.5 \\ C_{L} = 50  \text{pF} & 1.5 & 5.0 \\ C_{L} = 100  \text{pF} & 3.0 & 9.0 \\ C_{L} = 150  \text{pF} & 4.5 & 12.5 \\ C_{L} = 150  \text{pF} & 4.5 & 12.5 \\ C_{L} = 150  \text{pF} & 5 & 14 \\ C_{L} = 100  \text{pF} & 9 & 23 \\ C_{L} = 150  \text{pF} & 13 & 32 \\ C_{L} = 150  \text{pF} & 13 & 32 \\ C_{L} = 150  \text{pF} & 3 & 10 \\ C_{L} = 150  \text{pF} & 3.5 & 12 \\ C_{L} = 150  \text{pF} & 3.5 & 12 \\ C_{L} = 150  \text{pF} & 3.5 & 12 \\ C_{L} = 150  \text{pF} & 3.5 & 12 \\ C_{L} = 150  \text{pF} & 9 & 28 \\ C_{L} = 400  \text{pF} & 9 & 28 \\ C_{L} = 400  \text{pF} & 18 & 40 \\ C_{L} = 150  \text{pF} & 2.5 & 9 \\ C_{L} = 150  \text{pF} & 2.5 & 9 \\ C_{L} = 150  \text{pF} & 2.5 & 9 \\ C_{L} = 150  \text{pF} & 2.5 & 9 \\ C_{L} = 150  \text{pF} & 11 & 35 \\ C_{L} = 150  \text{pF} & 11 & 35 \\ C_{L} = 150  \text{pF} & 2.5 & 10 \\ C_{L} = 150  \text{pF} & 2.5 & 10 \\ C_{L} = 150  \text{pF} & 2.5 & 10 \\ C_{L} = 150  \text{pF} & 2.5 & 10 \\ C_{L} = 150  \text{pF} & 2.5 & 10 \\ C_{L} = 150  \text{pF} & 2.5 & 10 \\ C_{L} = 150  \text{pF} & 3 & 10 \\ C_{L} = 150  \text{pF} & 3 & 10 \\ C_{L} = 150  \text{pF} & 3 & 10 \\ C_{L} = 150  \text{pF} & 3 & 10 \\ C_{L} = 150  \text{pF} & 3 & 10 \\ C_{L} = 150  \text{pF} & 3 & 10 \\ C_{L} = 150  \text{pF} & 3 & 10 \\ C_{L} = 150  \text{pF} & 3 & 10 \\ C_{L} = 150  \text{pF} & 3 & 10 \\ C_{L} = 150  \text{pF} & 3 & 10 \\ C_{L} = 150  \text{pF} & 3 & 3 $	۱۲	Rise time, AWD, CLROUT, TDI, TDO, TMS, TMS2	C <sub>L</sub> = 100 pF	3.0	9.0	ns
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$			C <sub>L</sub> = 150 pF	4.5	2.5 5.0 9.0 12.5 2.5 5.0 9.0 12.5 8 14 23 32 10 12 21 28 40 8 9 25 35 45 10 25 45 65 10 25 45	
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$			C <sub>L</sub> = 15 pF	0.5	2.5	
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$		Fall times ANNID CLICOLITY TOU TOO TAKE TAKES	C <sub>L</sub> = 50 pF	1.5	5.0	
$t_{r}  \text{Rise time, } \overline{\text{RST}} \\ \\ \begin{aligned} & \begin{array}{c} C_L = 15  \text{pF} \\ C_L = 50  \text{pF} \\ \end{array} \\ & \begin{array}{c} 5 & 14 \\ C_L = 100  \text{pF} \\ \end{array} \\ & \begin{array}{c} 9 & 23 \\ C_L = 150  \text{pF} \\ \end{array} \\ & \begin{array}{c} 13 & 32 \\ \end{array} \\ \\ C_L = 150  \text{pF} \\ \end{array} \\ & \begin{array}{c} 13 & 32 \\ \end{array} \\ \\ C_L = 150  \text{pF} \\ \end{array} \\ & \begin{array}{c} 3 & 10 \\ C_L = 50  \text{pF} \\ \end{array} \\ & \begin{array}{c} 3.5 & 12 \\ \hline C_L = 150  \text{pF} \\ \end{array} \\ & \begin{array}{c} 3.5 & 12 \\ \hline C_L = 150  \text{pF} \\ \end{array} \\ & \begin{array}{c} 7 & 21 \\ \hline C_L = 150  \text{pF} \\ \end{array} \\ & \begin{array}{c} 9 & 28 \\ \hline C_L = 400  \text{pF} \\ \end{array} \\ & \begin{array}{c} 18 & 40 \\ \hline \end{array} \\ \\ \begin{array}{c} C_L = 150  \text{pF} \\ \end{array} \\ & \begin{array}{c} 2 & 8 \\ \hline C_L = 50  \text{pF} \\ \end{array} \\ & \begin{array}{c} 2 & 8 \\ \hline C_L = 50  \text{pF} \\ \end{array} \\ & \begin{array}{c} 2.5 & 9 \\ \hline C_L = 150  \text{pF} \\ \end{array} \\ \\ \begin{array}{c} 11 & 35 \\ \hline C_L = 150  \text{pF} \\ \end{array} \\ \\ \begin{array}{c} 11 & 35 \\ \hline C_L = 150  \text{pF} \\ \end{array} \\ \\ \begin{array}{c} 10 & 45 \\ \hline \end{array} \\ \\ \begin{array}{c} C_L = 150  \text{pF} \\ \end{array} \\ \\ \begin{array}{c} 10 & 45 \\ \hline \end{array} \\ \\ \begin{array}{c} C_L = 150  \text{pF} \\ \end{array} \\ \\ \begin{array}{c} 12 & 45 \\ \hline C_L = 150  \text{pF} \\ \end{array} \\ \\ \begin{array}{c} 12 & 45 \\ \hline C_L = 150  \text{pF} \\ \end{array} \\ \\ \begin{array}{c} 12 & 45 \\ \hline C_L = 150  \text{pF} \\ \end{array} \\ \\ \begin{array}{c} 12 & 45 \\ \hline C_L = 150  \text{pF} \\ \end{array} \\ \\ \begin{array}{c} 12 & 45 \\ \hline C_L = 150  \text{pF} \\ \end{array} \\ \\ \begin{array}{c} 12 & 45 \\ \hline C_L = 150  \text{pF} \\ \end{array} \\ \\ \begin{array}{c} 12 & 45 \\ \hline C_L = 150  \text{pF} \\ \end{array} \\ \\ \begin{array}{c} 12 & 45 \\ \hline C_L = 150  \text{pF} \\ \end{array} \\ \\ \begin{array}{c} 12 & 45 \\ \hline C_L = 150  \text{pF} \\ \end{array} \\ \\ \begin{array}{c} 12 & 45 \\ \hline C_L = 150  \text{pF} \\ \end{array} \\ \\ \begin{array}{c} 12 & 45 \\ \hline C_L = 150  \text{pF} \\ \end{array} \\ \\ \begin{array}{c} 12 & 45 \\ \hline C_L = 150  \text{pF} \\ \end{array} \\ \\ \begin{array}{c} 12 & 45 \\ \hline C_L = 150  \text{pF} \\ \end{array} \\ \\ \begin{array}{c} 12 & 45 \\ \hline C_L = 150  \text{pF} \\ \end{array} \\ \\ \begin{array}{c} 12 & 45 \\ \hline C_L = 150  \text{pF} \\ \end{array} \\ \\ \begin{array}{c} 12 & 45 \\ \hline C_L = 150  \text{pF} \\ \end{array} \\ \begin{array}{c} 12 & 45 \\ \hline C_L = 150  \text{pF} \\ \end{array} \\ \\ \begin{array}{c} 12 & 45 \\ \hline C_L = 150  \text{pF} \\ \end{array} \\ \\ \begin{array}{c} 12 & 45 \\ \hline C_L = 150  \text{pF} \\ \end{array} \\ \end{array} \\ \begin{array}{c} 12 & 45 \\ \hline C_L = 150  \text{pF} \\ \end{array} \\ \begin{array}{c} 12 & 45 \\ \hline C_L = 150  \text{pF} \\ \end{array} \\ \begin{array}{c} 12 & 45 \\ \hline C_L = 150  \text{pF} \\ \end{array} \\ \begin{array}{c} 12 & 45 \\ \hline C_L = 150  \text{pF} \\ \end{array} \\ \begin{array}{c} 12 & 45 \\ \hline C_L = 150  \text{pF} \\ \end{array} \\ \begin{array}{c} 12 & 45 \\ \hline C_L = 150  \text{pF} \\ \end{array} \\ \begin{array}{c} 12 & 45 \\ \hline C_L = 150  \text{pF} \\ \end{array} \\ \begin{array}{c} 12 & 45 \\ \hline C_L = 150  \text{pF} \\ \end{array} \\ \begin{array}{c} 12 & 45 \\ \hline C_L = 150  \text{pF} \\ \end{array} \\ \begin{array}{c} 12 & 45$	Ч	Fall time, AWD, CLKOUT, TDI, TDO, TMS, TMS2	C <sub>L</sub> = 100 pF	3.0	9.0	ns
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$			C <sub>L</sub> = 150 pF	4.5	12.5	
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$			C <sub>L</sub> = 15 pF	2.5	8	
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$		Disa time DOT	C <sub>L</sub> = 50 pF	5	14	
$t_{r}  \text{Rise time, 4mA, 5 V tolerant pins}  \begin{cases} C_{L} = 15 \text{ pF} & 3 & 10 \\ C_{L} = 50 \text{ pF} & 3.5 & 12 \\ C_{L} = 100 \text{ pF} & 7 & 21 \\ C_{L} = 150 \text{ pF} & 9 & 28 \\ C_{L} = 400 \text{ pF} & 18 & 40 \\ \end{cases}$ $t_{f}  \text{Fall time, 4mA, 5 V tolerant pins}  \begin{cases} C_{L} = 15 \text{ pF} & 2 & 8 \\ C_{L} = 50 \text{ pF} & 2.5 & 9 \\ C_{L} = 150 \text{ pF} & 2.5 & 9 \\ C_{L} = 100 \text{ pF} & 8 & 25 \\ C_{L} = 150 \text{ pF} & 11 & 35 \\ C_{L} = 150 \text{ pF} & 11 & 35 \\ C_{L} = 400 \text{ pF} & 2.5 & 10 \\ C_{L} = 400 \text{ pF} & 2.5 & 10 \\ C_{L} = 150 \text{ pF} & 6.0 & 25 \\ C_{L} = 100 \text{ pF} & 12 & 45 \\ C_{L} = 150 \text{ pF} & 18 & 65 \\ \end{cases}$ $t_{f}  \text{Fall time, all other output pins}  \begin{cases} C_{L} = 15 \text{ pF} & 3 & 10 \\ C_{L} = 50 \text{ pF} & 3 & 10 \\ C_{L} = 150 \text{ pF} & 3 & 10 \\ C_{L} = 150 \text{ pF} & 8.5 & 25 \\ C_{L} = 100 \text{ pF} & 16 & 45 \\ \end{cases}$	۱۲	Rise time, RS1	C <sub>L</sub> = 100 pF	9	23	ns
$t_{r}  \text{Rise time, 4mA, 5 V tolerant pins}  \begin{bmatrix} C_{L} = 50 \text{ pF} & 3.5 & 12 \\ C_{L} = 100 \text{ pF} & 7 & 21 \\ C_{L} = 150 \text{ pF} & 9 & 28 \\ C_{L} = 400 \text{ pF} & 18 & 40 \\ \end{bmatrix}  \text{ns}  t_{f}  \text{Fall time, 4mA, 5 V tolerant pins}  \begin{bmatrix} C_{L} = 15 \text{ pF} & 2 & 8 \\ C_{L} = 50 \text{ pF} & 2.5 & 9 \\ C_{L} = 100 \text{ pF} & 8 & 25 \\ C_{L} = 100 \text{ pF} & 11 & 35 \\ C_{L} = 100 \text{ pF} & 11 & 35 \\ C_{L} = 400 \text{ pF} & 2.5 & 10 \\ C_{L} = 400 \text{ pF} & 2.5 & 10 \\ C_{L} = 50 \text{ pF} & 2.5 & 10 \\ C_{L} = 150 \text{ pF} & 2.5 & 10 \\ C_{L} = 150 \text{ pF} & 12 & 45 \\ C_{L} = 150 \text{ pF} & 18 & 65 \\ \end{bmatrix}  \text{ns}  t_{f}  \text{Fall time, all other output pins}  \begin{bmatrix} C_{L} = 15 \text{ pF} & 3 & 10 \\ C_{L} = 150 \text{ pF} & 3 & 10 \\ C_{L} = 150 \text{ pF} & 3 & 10 \\ C_{L} = 50 \text{ pF} & 8.5 & 25 \\ C_{L} = 100 \text{ pF} & 8.5 & 25 \\ C_{L} = 100 \text{ pF} & 16 & 45 \\ \end{bmatrix}  \text{ns}  t_{f}  \text{ns}  t_{f}  \text{ns}  t_{f}  t_$			C <sub>L</sub> = 150 pF	13	32	
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$			C <sub>L</sub> = 15 pF	3	10	
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$			$C_{L} = 50 \text{ pF}$	3.5	12	
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	t <sub>r</sub>	Rise time,4mA, 5 V tolerant pins	C <sub>L</sub> = 100 pF	7	21	ns
$t_{f}  \text{Fall time, 4mA, 5 V tolerant pins}  \begin{bmatrix} C_{L} = 15 \text{ pF} & 2 & 8 \\ C_{L} = 50 \text{ pF} & 2.5 & 9 \\ C_{L} = 100 \text{ pF} & 8 & 25 \\ C_{L} = 150 \text{ pF} & 11 & 35 \\ C_{L} = 400 \text{ pF} & 20 & 45 \\ \end{bmatrix}$ ns $t_{r}  \text{Rise time, all other output pins}  \begin{bmatrix} C_{L} = 15 \text{ pF} & 2.5 & 10 \\ C_{L} = 50 \text{ pF} & 2.5 & 10 \\ C_{L} = 50 \text{ pF} & 6.0 & 25 \\ C_{L} = 100 \text{ pF} & 12 & 45 \\ C_{L} = 150 \text{ pF} & 18 & 65 \\ \end{bmatrix}$ ns $t_{f}  \text{Fall time, all other output pins}  \begin{bmatrix} C_{L} = 15 \text{ pF} & 3 & 10 \\ C_{L} = 50 \text{ pF} & 3 & 10 \\ C_{L} = 50 \text{ pF} & 8.5 & 25 \\ C_{L} = 100 \text{ pF} & 16 & 45 \\ \end{bmatrix}$ ns				9	28	
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$			$C_L = 400 \text{ pF}$	18	40	
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$			C <sub>L</sub> = 15 pF	2	8	
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$			C <sub>L</sub> = 50 pF	2.5	9	
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	t <sub>f</sub>	Fall time, 4mA, 5 V tolerant pins		8	25	ns
$t_{f} = \begin{cases} C_{L} = 15 \text{ pF} & 2.5 & 10 \\ C_{L} = 50 \text{ pF} & 6.0 & 25 \\ C_{L} = 100 \text{ pF} & 12 & 45 \\ C_{L} = 150 \text{ pF} & 18 & 65 \\ \end{cases}$ $t_{f} = \begin{cases} C_{L} = 15 \text{ pF} & 3 & 10 \\ C_{L} = 15 \text{ pF} & 3 & 10 \\ C_{L} = 50 \text{ pF} & 8.5 & 25 \\ C_{L} = 100 \text{ pF} & 16 & 45 \\ \end{cases}$				11	35	
			$C_{L} = 400 \text{ pF}$	20	45	
			C <sub>L</sub> = 15 pF	2.5	10	
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$		Disc time all other output pine	C <sub>L</sub> = 50 pF	6.0	25	
	۲r	Kise time, all other output pins		12	45	ns
$C_L = 50 \text{ pF}$ 8.5 25 $C_L = 100 \text{ pF}$ 16 45			C <sub>L</sub> = 150 pF	18	65	
$C_L = 100 \text{ pF}$ ns			C <sub>L</sub> = 15 pF	3	10	
$C_L = 100 \text{ pF}$ 16 45	<b>.</b>	Fall time, all other output pine	C <sub>L</sub> = 50 pF	8.5	25	20
$C_L = 150  pF$ 23 65	Ч	raii time, ali otnei output pins	C <sub>L</sub> = 100 pF	16	45	ns
			C <sub>L</sub> = 150 pF	23	65	

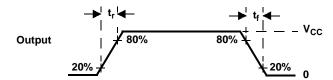


Figure 11. CMOS-Level Outputs

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### input timings

## timing requirements for input timings<sup>(1)</sup> (see Figure 12)

		MIN	MAX	UNIT
t <sub>pw</sub>	Input minimum pulse width	t <sub>c(ICLK)</sub> + 10		ns

<sup>1</sup>  $t_{c(ICLK)}$  = interface clock cycle time =  $1/f_{(ICLK)}$ 

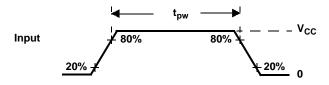


Figure 12. CMOS-Level Inputs

### flash timings

### timing requirements for program flash(1)

		MIN	TYP	MAX	UNIT
t <sub>prog(16-bit)</sub>	Half word (16-bit) programming time	4	16	200	μS
t <sub>prog(Total)</sub>	1M-byte programming time <sup>(2)</sup>		8	32	s
t <sub>erase(sector)</sub>	Sector erase time		7		S
t <sub>wec</sub>	Write/erase cycles at T <sub>A</sub> = 125°C	100	1000		cycles
$t_{fp(\overline{RST})}$	Flash pump settling time from RST to SLEEP		167t <sub>c(SYS)</sub>		ns
t <sub>fp(SLEEP)</sub>	Initial flash pump settling time from SLEEP to STANDBY	167t <sub>c(SYS)</sub>		ns	
t <sub>fp(STANDBY)</sub>	Initial flash pump settling time from STANDBY to ACTIVE	84t <sub>c(SYS)</sub>		ns	

<sup>1</sup> For more detailed information on the flash core sectors, see the "flash program and erase" section of this data sheet.



<sup>2</sup> The 1M-byte programming time includes overhead of state machine.

#### SPIn master mode timing parameters

## SPIn master mode external timing parameters (CLOCK PHASE = 0, SPInCLK = output, SPInSIMO = output, and SPInSOMI = input) $^{(1)(2)(3)}$ (see Figure 13)

NO.			MIN	MAX	UNIT
1	t <sub>c(SPC)M</sub>	Cycle time, SPInCLK (4)	100	256t <sub>c(ICLK)</sub>	
2 <sup>(5)</sup>	t <sub>w(SPCH)M</sub>	Pulse duration, SPInCLK high (clock polarity = 0)	$0.5t_{c(SPC)M} - t_r$	$0.5t_{c(SPC)M} + 5$	
2(-)	t <sub>w(SPCL)M</sub>	Pulse duration, SPInCLK low (clock polarity = 1)	$0.5t_{c(SPC)M} - t_f$	$0.5t_{c(SPC)M} + 5$	
3 <sup>(5)</sup>	t <sub>w(SPCL)M</sub>	Pulse duration, SPInCLK low (clock polarity = 0)	$0.5t_{c(SPC)M} - t_f$	$0.5t_{c(SPC)M} + 5$	
3(0)	t <sub>w(SPCH)M</sub>	Pulse duration, SPInCLK high (clock polarity = 1)	$0.5t_{c(SPC)M} - t_r$	$0.5t_{c(SPC)M} + 5$	
4(5)	t <sub>d(SPCH-SIMO)M</sub>	Delay time, SPInCLK high to SPInSIMO valid (clock polarity = 0)		10	
4(9)	t <sub>d(SPCL-SIMO)M</sub>	Delay time, SPInCLK low to SPInSIMO valid (clock polarity = 1)		10	ns
5 <sup>(5)</sup>	t <sub>v(SPCL-SIMO)M</sub>	Valid time, SPInSIMO data valid after SPInCLK low (clock polarity = 0)	$t_{C(SPC)M} - 5 - t_f$		
5(-7	$t_{V(SPCH-SIMO)M}$	Valid time, SPInSIMO data valid after SPInCLK high (clock polarity = 1)	$t_{c(SPC)M} - 5 - t_r$		
6 <sup>(5)</sup>	t <sub>su(SOMI-SPCL)M</sub>	Setup time, SPInSOMI before SPInCLK low (clock polarity = 0)	6		
6(3)	t <sub>su(SOMI-SPCH)M</sub>	Setup time, SPInSOMI before SPInCLK high (clock polarity = 1)	6		
7 <sup>(5)</sup>	t <sub>v(SPCL-SOMI)M</sub>	Valid time, SPInSOMI data valid after SPInCLK low (clock polarity = 0)	4		
/\-'	t <sub>v(SPCH-SOMI)M</sub>	Valid time, SPInSOMI data valid after SPInCLK high (clock polarity = 1)	4		

<sup>1</sup> The MASTER bit (SPInCTRL2.3) is set and the CLOCK PHASE bit (SPInCTRL2.0) is cleared.

For PS values from 1 to 255:  $t_{c(SPC)M} \ge (PS + 1)t_{c(ICLK)} \ge 100$  ns, where PS is the prescale value set in the SPInCTL1.[12:5] register bits.

For PS values of 0:  $t_{\text{c(SPC)M}} = 2t_{\text{c(ICLK)}} \geq 100 \text{ ns.}$ 

5 The active edge of the SPInCLK signal referenced is controlled by the CLOCK POLARITY bit (SPInCTRL2.1).



<sup>2</sup>  $t_{c(ICLK)}$  = interface clock cycle time =  $1/f_{(ICLK)}$ 

<sup>3</sup> For rise and fall timings, see the "switching characteristics for output timings versus load capacitance" table.

<sup>4</sup> When the SPI is in master mode, the following must be true:

### SPIn master mode timing parameters (continued)

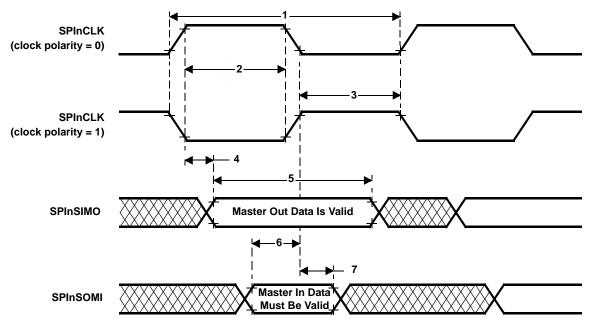


Figure 13. SPIn Master Mode External Timing (CLOCK PHASE = 0)



#### SPIn master mode timing parameters (continued)

## SPIn master mode external timing parameters (CLOCK PHASE = 1, SPInCLK = output, SPInSIMO = output, and SPInSOMI = input)<sup>(1)(2)(3)</sup> (see Figure 14)

NO.			MIN	MAX	UNIT
1	t <sub>c(SPC)M</sub>	Cycle time, SPInCLK (4)	100	256t <sub>c(ICLK)</sub>	
2 <sup>(5)</sup>	t <sub>w(SPCH)M</sub>	Pulse duration, SPInCLK high (clock polarity = 0)	$0.5t_{c(SPC)M} - t_r$	$0.5t_{c(SPC)M} + 5$	
2(0)	t <sub>w(SPCL)M</sub>	Pulse duration, SPInCLK low (clock polarity = 1)	$0.5t_{C(SPC)M} - t_f$	0.5t <sub>c(SPC)M</sub> + 5	
3 <sup>(5)</sup>	t <sub>w(SPCL)M</sub>	Pulse duration, SPInCLK low (clock polarity = 0)	$0.5t_{C(SPC)M} - t_f$	0.5t <sub>c(SPC)M</sub> + 5	
3(0)	t <sub>w(SPCH)M</sub>	Pulse duration, SPInCLK high (clock polarity = 1)	$0.5t_{c(SPC)M} - t_r$	0.5t <sub>c(SPC)M</sub> + 5	
4 <sup>(5)</sup>	t <sub>v(SIMO-SPCH)M</sub>	Valid time, SPInCLK high after SPInSIMO data valid (clock polarity = 0)	0.5t <sub>c(SPC)M</sub> - 10		
	t <sub>v</sub> (SIMO-SPCL)M	Valid time, SPInCLK low after SPInSIMO data valid (clock polarity = 1)	0.5t <sub>c(SPC)M</sub> - 10		ns
5 <sup>(5)</sup>	t <sub>v</sub> (SPCH-SIMO)M	Valid time, SPInSIMO data valid after SPInCLK high (clock polarity = 0)	$0.5t_{\text{c(SPC)M}} - 5 - t_{\text{r}}$		
5(0)	t <sub>v</sub> (SPCL-SIMO)M	Valid time, SPInSIMO data valid after SPInCLK low (clock polarity = 1)	$0.5t_{c(SPC)M} - 5 - t_{f}$		
6 <sup>(5)</sup>	t <sub>su(SOMI-SPCH)M</sub>	Setup time, SPInSOMI before SPInCLK high (clock polarity = 0)	6		
6(0)	t <sub>su(SOMI-SPCL)M</sub>	Setup time, SPInSOMI before SPInCLK low (clock polarity = 1)	6		
7(5)	t <sub>v</sub> (SPCH-SOMI)M	Valid time, SPInSOMI data valid after SPInCLK high (clock polarity = 0)	4		
1(0)	t <sub>v(SPCL-SOMI)M</sub>	Valid time, SPInSOMI data valid after SPInCLK low (clock polarity = 1)	4		

<sup>1</sup> The MASTER bit (SPInCTRL2.3) is set and the CLOCK PHASE bit (SPInCTRL2.0) is set.

For PS values from 1 to 255:  $t_{c(SPC)M} \geq (PS + 1)t_{c(ICLK)} \geq 100 \text{ ns, where PS is the prescale value set in the SPInCTL1.} \\ t_{c(SPC)M} = 2t_{c(ICLK)} \geq 100 \text{ ns.} \\ t_{c(SPC)M} = 2t_{c(I$ 

5 The active edge of the SPInCLK signal referenced is controlled by the CLOCK POLARITY bit (SPInCTRL2.1).



<sup>2</sup>  $t_{c(ICLK)}$  = interface clock cycle time =  $1/f_{(ICLK)}$ 

<sup>3</sup> For rise and fall timings, see the "switching characteristics for output timings versus load capacitance" table.

<sup>4</sup> When the SPI is in master mode, the following must be true:

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## SPIn master mode timing parameters (continued)

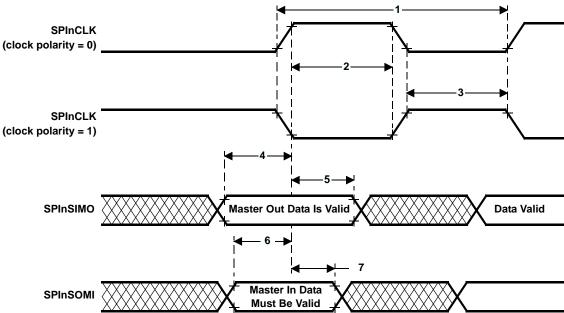


Figure 14. SPIn Master Mode External Timing (CLOCK PHASE = 1)

#### SPIn slave mode timing parameters

## SPIn slave mode external timing parameters (CLOCK PHASE = 0, SPInCLK = input, SPInSIMO = input, and SPInSOMI = output) $^{(1)(2)(3)(4)}$ (see Figure 15)

NO			MIN	MAX	UNIT
1	t <sub>c(SPC)S</sub>	Cycle time, SPInCLK <sup>(5)</sup>	100	256t <sub>c(ICLK)</sub>	
2 <sup>(6)</sup>	t <sub>w(SPCH)S</sub>	Pulse duration, SPInCLK high (clock polarity = 0)	$0.5t_{c(SPC)S} - 0.25t_{c(ICLK)}$	$0.5t_{c(SPC)S} + 0.25t_{c(ICLK)}$	
2(-)	t <sub>w(SPCL)S</sub>	Pulse duration, SPInCLK low (clock polarity = 1)	$0.5t_{c(SPC)S} - 0.25t_{c(ICLK)}$	$0.5t_{c(SPC)S} + 0.25t_{c(ICLK)}$	
3(6)	t <sub>w(SPCL)S</sub>	Pulse duration, SPInCLK low (clock polarity = 0)	$0.5t_{c(SPC)S} - 0.25t_{c(ICLK)}$	$0.5t_{c(SPC)S} + 0.25t_{c(ICLK)}$	
3(0)	t <sub>w(SPCH)S</sub>	Pulse duration, SPInCLK high (clock polarity = 1)	$0.5t_{C(SPC)S} - 0.25t_{C(ICLK)}$	$0.5t_{c(SPC)S} + 0.25t_{c(ICLK)}$	
4 <sup>(6)</sup>	t <sub>d(SPCH-SOMI)S</sub>	Delay time, SPInCLK high to SPInSOMI valid (clock polarity = 0)		6 + t <sub>r</sub>	
4(0)	t <sub>d(SPCL-SOMI)S</sub>	Delay time, SPInCLK low to SPInSOMI valid (clock polarity = 1)		6 + t <sub>f</sub>	
5 <sup>(6)</sup>	t <sub>v(SPCH-SOMI)S</sub>	Valid time, SPInSOMI data valid after SPInCLK high (clock polarity = 0)	$t_{c(SPC)S} - 6 - t_r$		ns
5(0)	t <sub>v(SPCL-SOMI)S</sub>	Valid time, SPInSOMI data valid after SPInCLK low (clock polarity = 1)	$t_{c(SPC)S} - 6 - t_f$		
6 <sup>(6)</sup>	t <sub>su(SIMO-SPCL)S</sub>	Setup time, SPInSIMO before SPInCLK low (clock polarity = 0)	6		
6(0)	t <sub>su(SIMO-SPCH)S</sub>	Setup time, SPInSIMO before SPInCLK high (clock polarity = 1)	6		
7(6)	t <sub>v(SPCL-SIMO)S</sub>	Valid time, SPInSIMO data valid after SPInCLK low (clock polarity = 0)	6		
1,0)	t <sub>v(SPCH-SIMO)S</sub>	Valid time, SPInSIMO data valid after SPInCLK high (clock polarity = 1)	6		

- 1 The MASTER bit (SPInCTRL2.3) is cleared and the CLOCK PHASE bit (SPInCTRL2.0) is cleared.
- 2 If the SPI is in slave mode, the following must be true:  $t_{c(SPC)S} \ge (PS + 1) t_{c(ICLK)}$ , where PS = prescale value set in SPInCTL1.[12:5].
- 3 For rise and fall timings, see the "switching characteristics for output timings versus load capacitance" table.
- 4  $t_{c(ICLK)}$  = interface clock cycle time =  $1/f_{(ICLK)}$
- 5 When the SPIn is in slave mode, the following must be true:

For PS values from 1 to 255:  $t_{c(SPC)S} \ge (PS+1)t_{c(ICLK)} \ge 100 \text{ ns, where PS is the prescale value set in the SPInCTL1.} [12:5] \text{ register bits.}$ 

For PS values of 0:  $t_{\text{c(SPC)S}} = 2t_{\text{c(ICLK)}} \ge 100 \text{ ns.}$ 

6The active edge of the SPInCLK signal referenced is controlled by the CLOCK POLARITY bit (SPInCTRL2.1).



### SPIn slave mode timing parameters (continued)

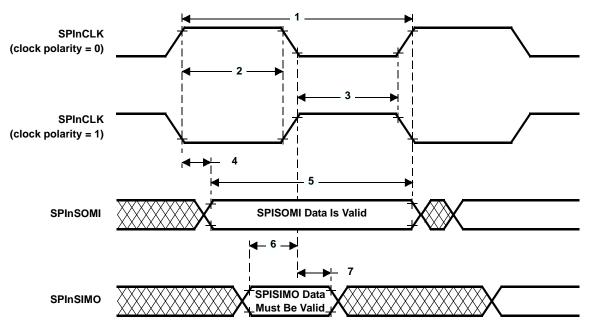


Figure 15. SPIn Slave Mode External Timing (CLOCK PHASE = 0)



#### SPIn slave mode timing parameters (continued)

## SPIn slave mode external timing parameters (CLOCK PHASE = 1, SPInCLK = input, SPInSIMO = input, and SPInSOMI = output) $^{(1)(2)(3)(4)}$ (see Figure 16)

NO			MIN	MAX	UNIT
1	t <sub>c(SPC)S</sub>	Cycle time, SPInCLK <sup>(5)</sup>	100	256t <sub>c(ICLK)</sub>	
2 <sup>(6)</sup>	t <sub>w(SPCH)S</sub>	Pulse duration, SPInCLK high (clock polarity = 0)	$0.5t_{c(SPC)S}$ $-0.25t_{c(ICLK)}$	$0.5t_{c(SPC)S} + 0.25t_{c(ICLK)}$	
2(0)	t <sub>w(SPCL)S</sub>	Pulse duration, SPInCLK low (clock polarity = 1)	$0.5t_{c(SPC)S}$ $-0.25t_{c(ICLK)}$	$0.5t_{c(SPC)S} + 0.25t_{c(ICLK)}$	
3 <sup>(6)</sup>	t <sub>w(SPCL)S</sub>	Pulse duration, SPInCLK low (clock polarity = 0)	$0.5t_{c(SPC)S}$ $-0.25t_{c(ICLK)}$	$0.5t_{c(SPC)S} + 0.25t_{c(ICLK)}$	
3(0)	t <sub>w(SPCH)S</sub>	Pulse duration, SPInCLK high (clock polarity = 1)	$0.5t_{c(SPC)S}$ $-0.25t_{c(ICLK)}$	$0.5t_{c(SPC)S} + 0.25t_{c(ICLK)}$	
4 <sup>(6)</sup>	t <sub>v(SOMI-SPCH)S</sub>	Valid time, SPInCLK high after SPInSOMI data valid (clock polarity = 0)	$0.5t_{\text{c(SPC)S}} - 6 - t_{\text{r}}$		
4(0)	t <sub>v(SOMI-SPCL)S</sub>	Valid time, SPInCLK low after SPInSOMI data valid (clock polarity = 1)	$0.5t_{\text{C(SPC)S}} - 6 - t_{\text{f}}$		
5 <sup>(6)</sup>	t <sub>v(SPCH-SOMI)S</sub>	Valid time, SPInSOMI data valid after SPInCLK high (clock polarity = 0)	$0.5t_{C(SPC)S}-6-t_r$		ns
5(0)	t <sub>V(SPCL-SOMI)S</sub>	Valid time, SPInSOMI data valid after SPInCLK low (clock polarity = 1)	$0.5t_{\text{C(SPC)S}} - 6 - t_{\text{f}}$		
6 <sup>(6)</sup>	t <sub>su(SIMO-SPCH)S</sub>	Setup time, SPInSIMO before SPInCLK high (clock polarity = 0)	6		
6(3)	t <sub>su(SIMO-SPCL)S</sub>	Setup time, SPInSIMO before SPInCLK low (clock polarity = 1)	6		
7(6)	t <sub>v(SPCH-SIMO)S</sub>	Valid time, SPInSIMO data valid after SPInCLK high (clock polarity = 0)	6		
1(0)	t <sub>v(SPCL-SIMO)S</sub>	Valid time, SPInSIMO data valid after SPInCLK low (clock polarity = 1)	6		

<sup>1</sup> The MASTER bit (SPInCTRL2.3) is cleared and the CLOCK PHASE bit (SPInCTRL2.0) is set.

For PS values from 1 to 255:  $t_{c(SPC)S} \geq (PS + 1)t_{c(ICLK)} \geq 100 \text{ ns, where PS is the prescale value set in the SPInCTL1.} \\ [12:5] \text{ register bits.}$ 

For PS values of 0:  $t_{c(SPC)S} = 2t_{c(ICLK)} \ge 100 \text{ ns.}$ 

6 The active edge of the SPInCLK signal referenced is controlled by the CLOCK POLARITY bit (SPInCTRL2.1).



<sup>2</sup> If the SPI is in slave mode, the following must be true:  $t_{c(SPC)S} \ge (PS + 1) t_{c(ICLK)}$ , where PS = prescale value set in SPInCTL1.[12:5].

<sup>3</sup> For rise and fall timings, see the "switching characteristics for output timings versus load capacitance" table.

<sup>4</sup>  $t_{c(ICLK)}$  = interface clock cycle time =  $1/f_{(ICLK)}$ 

<sup>5</sup> When the SPIn is in slave mode, the following must be true:

## SPIn slave mode timing parameters (continued)

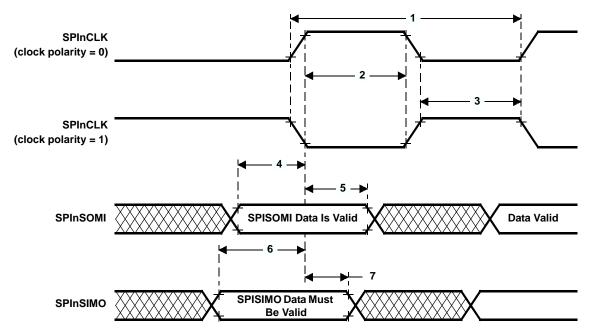


Figure 16. SPIn Slave Mode External Timing (CLOCK PHASE = 1)

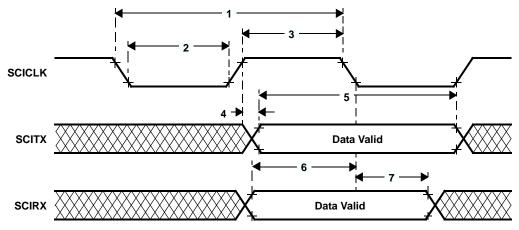


### SCIn isosynchronous mode timings — internal clock

## timing requirements for internal clock SCIn isosynchronous mode<sup>(1)(2)(3)</sup> (see Figure 17)

NO.			(BAUD + 1) IS EVEN OR BAUD = 0		(BAUD IS ODD AND	,	UNIT
			MIN	MAX	MIN	MAX	
1	t <sub>c(SCC)</sub>	Cycle time, SCInCLK	2t <sub>c(ICLK)</sub>	$2^{24}t_{c(ICLK)}$	3t <sub>c(ICLK)</sub>	(2 <sup>24</sup> –1) t <sub>c(ICLK)</sub>	ns
2	t <sub>w(SCCL)</sub>	Pulse duration, SCInCLK low	$0.5t_{c(SCC)} - t_f$	0.5t <sub>c(SCC)</sub> + 5	$0.5t_{c(SCC)} + 0.5t_{c(ICLK)} - t_f$	$0.5t_{c(SCC)} + 0.5t_{c(ICLK)}$	ns
3	t <sub>w(SCCH)</sub>	Pulse duration, SCInCLK high	$0.5t_{c(SCC)} - t_r$	0.5t <sub>c(SCC)</sub> + 5	$0.5t_{c(SCC)}$ $-0.5t_{c(ICLK)}$ $-t_r$	$0.5t_{c(SCC)} - 0.5t_{c(ICLK)}$	ns
4	t <sub>d(SCCH-TXV)</sub>	Delay time, SCInCLK high to SCInTX valid		10		10	ns
5	t <sub>v(TX)</sub>	Valid time, SCInTX data after SCInCLK low	t <sub>c(SCC)</sub> - 10		t <sub>c(SCC)</sub> - 10		ns
6	t <sub>su(RX-SCCL)</sub>	Setup time, SCInRX before SCInCLK low	$t_{c(ICLK)} + t_f + 20$		$t_{c(ICLK)} + t_f + 20$		ns
7	t <sub>v(SCCL-RX)</sub>	Valid time, SCInRX data after SCInCLK low	- t <sub>c(ICLK)</sub> + t <sub>f</sub> + 20		- t <sub>c(ICLK)</sub> + t <sub>f</sub> + 20		ns

- 1 BAUD = 24-bit concatenated value formed by the SCI[H,M,L]BAUD registers.
- 2  $t_{c(ICLK)}$  = interface clock cycle time =  $1/f_{(ICLK)}$
- 3 For rise and fall timings, see the "switching characteristics for output timings versus load capacitance" table.



NOTE: Data transmission/reception characteristics for isosynchronous mode with internal clocking are similar to the asynchronous mode. Data transmission occurs on the SCICLK rising edge, and data reception on the SCICLK falling edge.

Figure 17. SCIn Isosynchronous Mode Timing Diagram for Internal Clock



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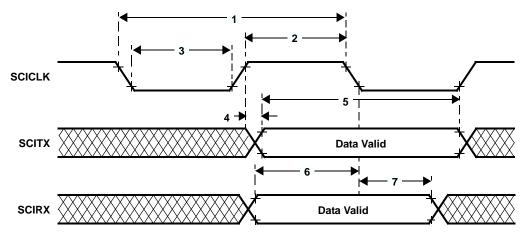
#### SCIn isosynchronous mode timings — external clock

#### timing requirements for external clock SCIn isosynchronous mode<sup>(1)(2)</sup> (see Figure 18)

NO.			MIN	MAX	UNIT
1	t <sub>c(SCC)</sub>	Cycle time, SCInCLK <sup>(3)</sup>	8t <sub>c(ICLK)</sub>		ns
2	t <sub>w(SCCH)</sub>	Pulse duration, SCInCLK high	$0.5t_{c(SCC)} - 0.25t_{c(ICLK)}$	$0.5t_{c(SCC)} + 0.25t_{c(ICLK)}$	ns
3	t <sub>w(SCCL)</sub>	Pulse duration, SCInCLK low	$0.5t_{c(SCC)} - 0.25t_{c(ICLK)}$	$0.5t_{c(SCC)} + 0.25t_{c(ICLK)}$	ns
4	t <sub>d(SCCH-TXV)</sub>	Delay time, SCInCLK high to SCInTX valid		$2t_{c(ICLK)} + 12 + t_r$	ns
5	t <sub>v(TX)</sub>	Valid time, SCInTX data after SCInCLK low	2t <sub>c(SCC)</sub> -10		ns
6	t <sub>su(RX-SCCL)</sub>	Setup time, SCInRX before SCInCLK low	0		ns
7	t <sub>v(SCCL-RX)</sub>	Valid time, SCInRX data after SCInCLK low	2t <sub>c(ICLK)</sub> + 10		ns

<sup>1</sup>  $t_{c(ICLK)}$  = interface clock cycle time =  $1/f_{(ICLK)}$ 

<sup>3</sup> When driving an external SCInCLK, the following must be true:  $t_{c(SCC)} \ge 8t_{c(ICLK)}$ .



NOTE: Data transmission/reception characteristics for isosynchronous mode with external clocking are similar to the asynchronous mode. Data transmission occurs on the SCICLK rising edge, and data reception on the SCICLK falling edge.

Figure 18. SCIn Isosynchronous Mode Timing Diagram for External Clock



<sup>2</sup> For rise and fall timings, see the "switching characteristics for output timings versus load capacitance" table.

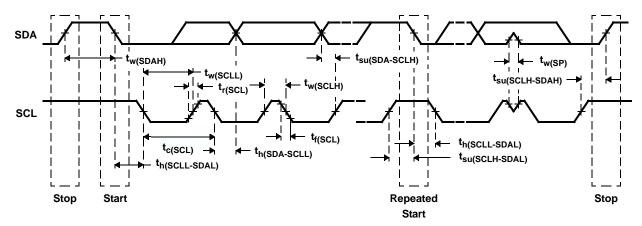
#### **I2C** timing

Table 11 assumes testing over recommended operating conditions.

Table 11. I2C Signals (SDA and SCL) Switching Characteristics<sup>(1)</sup>

	PARAMETER		STANI MO		FAST N	IODE	UNIT
			MIN	MAX	MIN	MAX	
t <sub>c(I2CCLK)</sub>	Cycle time, I2C module clock		75	150	75	150	ns
t <sub>c(SCL)</sub>	Cycle time, SCL		10		2.5		μS
t <sub>su(SCLH-SDAL)</sub>	Setup time, SCL high before SDA low (for a repeated STAR	T condition)	4.7		0.6		μS
t <sub>h(SCLL-SDAL)</sub>	Hold time, SCL low after SDA low (for a repeated START co	ndition)	4		0.6		μS
t <sub>w(SCLL)</sub>	SCLL) Pulse duration, SCL low				1.3		μS
t <sub>w(SCLH)</sub>	Pulse duration, SCL high		4		0.6		μS
t <sub>su(SDA-SCLH)</sub>	Setup time, SDA valid before SCL high		250		100		ns
t <sub>h(SDA-SCLL)</sub>	Hold time, SDA valid after SCL low	For I2C bus devices	0	3.45 <sup>(2)</sup>	0	0.9	μS
t <sub>w(SDAH)</sub>	Pulse duration, SDA high between STOP and START condit	ions	4.7		1.3		μS
t <sub>su(SCLH-SDAH)</sub>	Setup time, SCL high before SDA high (for STOP condition)		4.0		0.6		μS
t <sub>w(SP)</sub>	Pulse duration, spike (must be suppressed)				0	50	ns
C <sub>b</sub> <sup>(3)</sup>	Capacitive load for each bus line			400		400	pF

- 1 The I2C pins SDA and SCL do not feature fail-safe I/O buffers. These pins could potentially draw current when the device is powered down.
- $2 \ \, \text{The maximum } t_{h(SDA\text{-}SCLL)} \text{ for I2C bus devices needs only be met if the device does not stretch the low period } (t_{w(SCLL)}) \text{ of the SCL signal.}$
- 3  $C_b$  = The total capacitance of one bus line in pF.



NOTE:. A device must internally provide a hold time of at least 300 ns for the SDA signal (referred to the V<sub>IHmin</sub> of the SCL signal) to bridge the undefined region of the falling edge of SCL.

NOTE:. The maximum  $t_{h(SDA-SCLL)}$  needs only be met if the device does not stretch the LOW period  $(t_{w(SCLL)})$  of the SCL signal.

NOTE:. A fast-mode I2C-bus device can be used in a standard-mode I2C-bus system, but the requirement  $t_{su(SDA-SCLH)} \ge 250$  ns must then be met. This will automatically be the case if the device does not stretch the LOW period of the SCL signal. If such a device does stretch the LOW period of the SCL signal, it must output the next data bit to the SDA line  $t_r$  max +  $t_{su(SDA-SCLH)}$ .

NOTE:. C<sub>b</sub> = total capacitance of one bus line in pF. If mixed with fast-mode devices, faster fall-times are allowed.

Figure 19. I2C Timings



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### standard CAN controller (SCC) mode timings

### dynamic characteristics for the CANSTX and CANSRX pins

	PARAMETER	MIN	MAX	UNIT
$t_d$ (CANSTX)	Delay time, transmit shift register to CANSTX pin <sup>(1)</sup>		15	ns
t <sub>d</sub> (CANSRX)	Delay time, CANSRX pin to receive shift register		5	ns

<sup>1</sup> These values do not include the rise/fall times of the output buffer.

# expansion bus timing parameters, –40°C $\leq$ $T_{J}$ $\leq$ 150°C, 3.0 V $\leq$ $V_{CC}$ $\leq$ 3.6 V (see figure 20 and figure 21)

NO.		PARAMETER	MIN	MAX	UNIT
1	t <sub>c(CO)</sub>	Cycle time, CLKOUT	20.8		ns
2	t <sub>d(COH-EBADV)</sub>	Delay Time, CLKOUT high to EBADDR valid		21.4	ns
3	t <sub>h(COH-EBADIV)</sub>	Hold Time, EBADDR invalid after CLKOUT high		12.4	ns
4	t <sub>d(COH-EBOE)</sub>	Delay Time, CLKOUT high to EBOE fall		11.4	ns
5	t <sub>h(COH-EBOEH)</sub>	Hold Time, EBOE rise after CLKOUT high		11.4	ns
6	t <sub>d(COL-EBWR)</sub>	Delay Time, CLKOUT low to write strobe (EBWR) low		11.3	ns
7	t <sub>h(COL-EBWRH)</sub>	Hold Time, EBWR high after CLKOUT low		11.6	ns
8	t <sub>su(EBRDATV-COH)</sub>	Setup time, EBDATA valid before CLKOUT high (READ) <sup>(1)</sup>	15.2		ns
9	t <sub>h(COH-EBRDATIV)</sub>	Hold time, EBDATA invalid after CLKOUT high (READ)		(- 14.7)	ns
10	t <sub>d(COL-EBWDATV)</sub>	Delay time, CLKOUT low to EBDATA valid (WRITE)(2)		16.1	ns
11	t <sub>h(COL-EBWDATIV)</sub>	Hold time, EBDATA invalid after CLKOUT low (WRITE)		14.7	ns
		SECONDARY TIMES			
12	t <sub>d(COH-EBCS0)</sub>	Delay, CLKOUT high to EBCS0 fall		13.6	ns
13	t <sub>h(COH-EBCS0H)</sub>	Hold, EBCS0 rise after CLKOUT high		13.2	ns
14	t <sub>su(COH-EBHOLDL)</sub>	Setup time, EBHOLD low to CLKOUT high <sup>(1)</sup>	10.9		ns
15	t <sub>su(COH-EBHOLDH)</sub>	Setup time, EBHOLD high to CLKOUT high <sup>(1)</sup>	10.5	_	ns

<sup>1</sup> Setup time is the minimum time under worst case conditions. Data with less setup time will not work.



<sup>2</sup> Valid after CLKOUT goes low for write cycles.

## expansion bus module timing

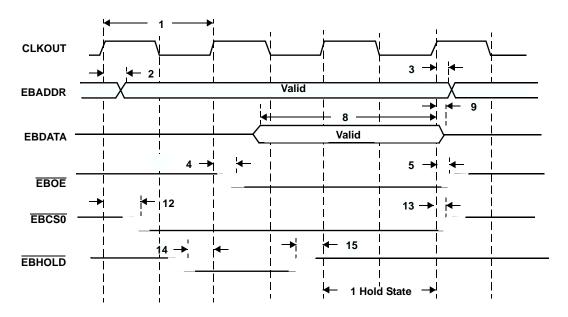


Figure 20. Expansion Memory Signal Timing—Reads

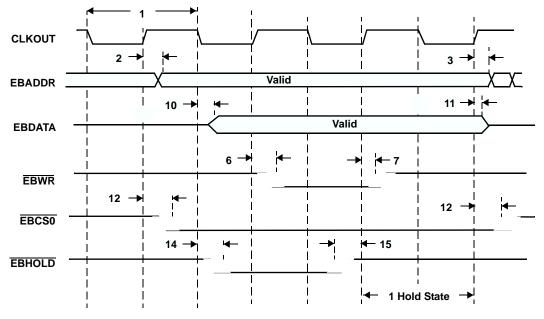


Figure 21. Expansion Memory Signal Timing —Writes

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#### high-end timer (HET) timings

#### minimum PWM output pulse width:

This is equal to one high resolution clock period (HRP). The HRP is defined by the 6-bit high resolution prescale factor (hr), which is user defined, giving prescale factors of 1 to 64, with a linear increment of codes.

Therefore, the minimum PWM output pulse width = HRP(min) = hr(min)/SYSCLK = 1/SYSCLK

For example, for a SYSCLK of 30 MHz, the minimum PWM output pulse width = 1/30 = 33.33ns

#### minimum input pulses we can capture:

The input pulse width must be greater or equal to the low resolution clock period (LRP), i.e., the HET loop (the HET program must fit within the LRP). The LRP is defined by the 3-bit loop-resolution prescale factor (Ir), which is user defined, with a power of 2 increment of codes. That is, the value of Ir can be 1, 2, 4, 8, 16, or 32.

Therefore, the minimum input pulse width = LRP(min) = hr(min) \* Ir(min)/SYSCLK = 1 \* 1/SYSCLK

For example, with a SYSCLK of 30 MHz, the minimum input pulse width = 1 \* 1/30 = 33.33 ns

#### **NOTE**

Once the input pulse width is greater than LRP, the resolution of the measurement is still HRP. (That is, the captured value gives the number of HRP clocks inside the pulse.)

#### Abbreviations:

hr = HET high resolution divide rate = 1, 2, 3,...63, 64

Ir = HET low resolution divide rate = 1, 2, 4, 8, 16, 32

High resolution clock period = HRP = hr/SYSCLK

Loop resolution clock period = LRP = hr\*lr/SYSCLK



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#### multi-buffered A-to-D converter (MibADC)

The multi-buffered A-to-D converter (MibADC) has a separate power bus for its analog circuitry that enhances the A-to-D performance by preventing digital switching noise on the logic circuitry, which could be present on  $V_{SS}$  and  $V_{CC}$ , from coupling into the A-to-D analog stage. All A-to-D specifications are given with respect to  $AD_{REFLO}$  unless otherwise noted.

#### MibADC recommended operating conditions(1)

		MIN	MAX	UNIT
AD <sub>REFHI</sub>	A-to-D high -voltage reference source	V <sub>SSAD</sub>	$V_{CCAD}$	V
AD <sub>REFLO</sub>	A-to-D low-voltage reference source	V <sub>SSAD</sub>	V <sub>CCAD</sub>	V
$V_{AI}$	Analog input voltage	V <sub>SSAD</sub> - 0.3	V <sub>CCAD</sub> + 0.3	V
I <sub>AIC</sub>	Analog input clamp current <sup>(2)</sup> $(V_{AI} < V_{SSAD} - 0.3 \text{ or } V_{AI} > V_{CCAD} + 0.3)$	- 2	2	mA

<sup>1</sup> For V<sub>CCAD</sub> and V<sub>SSAD</sub> recommended operating conditions, see the "device recommended operating conditions" table.

## operating characteristics over full ranges of recommended operating conditions<sup>(1)(2)</sup>

	PARAMETER	DESCRIPTION/CONDITIONS		MIN	TYP	MAX	UNIT
R <sub>i</sub>	Analog input resistance	See Figure 22.			250	500	Ω
C <sub>i</sub>	Analog input conscitance	Soo Figure 22	Conversion			10	рF
O <sub>i</sub>	Analog input capacitance	See Figure 22.	Sampling			30	pF
I <sub>AIL</sub>	Analog input leakage current	See Figure 22.		-1		1	μΑ
I <sub>ADREFHI</sub>	AD <sub>REFHI</sub> input current	AD <sub>REFHI</sub> = 3.6 V, AD <sub>REFLO</sub>	<sub>D</sub> = V <sub>SSAD</sub>			5	mA
CR	Conversion range over which specified accuracy is maintained	AD <sub>REFHI</sub> – AD <sub>REFLO</sub>				3.6	V
E <sub>DNL</sub>	Differential nonlinearity error	Difference between the actual step width and the ideal value. See Figure 23.				±1.5	LSB
E <sub>INL</sub>	Integral nonlinearity error	Maximum deviation from the best straight line through the MibADC. MibADC transfer characteristics, excluding the quantization error.  See Figure 24.				±2	LSB
E <sub>TOT</sub>	Total error/Absolute accuracy	Maximum value of the difference between an analog value and the ideal midstep value. See Figure 25.				±2	LSB

<sup>1</sup>  $V_{CCAD} = AD_{REFHI}$ 



<sup>2</sup> Input currents into any ADC input channel outside the specified limits could affect conversion results of other channels.

<sup>2 1</sup> LSB =  $(AD_{REFHI} - AD_{REFLO})/2^{10}$  for the MibADC

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#### multi-buffered A-to-D converter (MibADC) (continued)

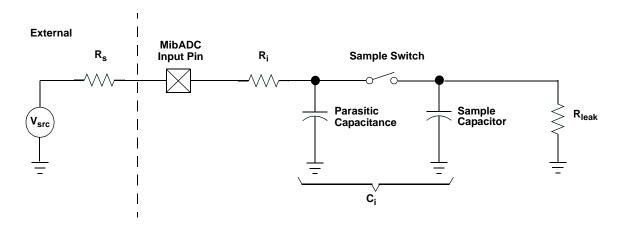


Figure 22. MibADC Input Equivalent Circuit

### multi-buffer ADC timing requirements

		MIN	NOM	MAX	UNIT
t <sub>c(ADCLK)</sub>	Cycle time, MibADC clock	0.05			μS
t <sub>d(SH)</sub>	Delay time, sample and hold time	1			μS
$t_{d(C)}$	Delay time, conversion time	0.55			μS
t <sub>d(SHC)</sub> <sup>(1)</sup>	Delay time, total sample/hold and conversion time	1.55			μS

<sup>1</sup> This is the minimum sample/hold and conversion time that can be achieved. These parameters are dependent on many factors; for more details, see the TMS470R1x Multi-Buffered Analog-to-Digital Converter (MibADC) Reference Guide (literature number SPNU206).



#### multi-buffered A-to-D converter (MibADC) (continued)

The differential nonlinearity error shown in Figure 23 (sometimes referred to as differential linearity) is the difference between an actual step width and the ideal value of 1 LSB.

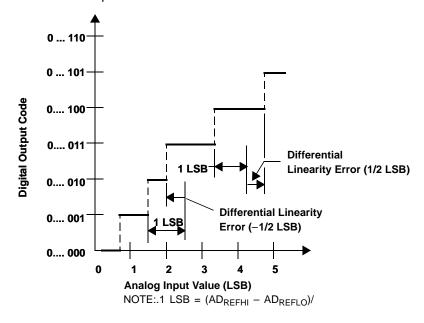


Figure 23. Differential Nonlinearity (DNL)

The integral nonlinearity error shown in Figure 24 (sometimes referred to as linearity error) is the deviation of the values on the actual transfer function from a straight line.

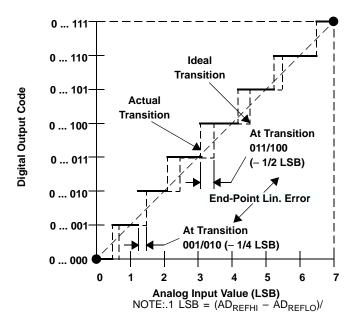


Figure 24. Integral Nonlinearity (INL) Error



#### multi-buffer A-to-D converter (MibADC) (continued)

The absolute accuracy or total error of an MibADC as shown in Figure 25 is the maximum value of the difference between an analog value and the ideal midstep value.

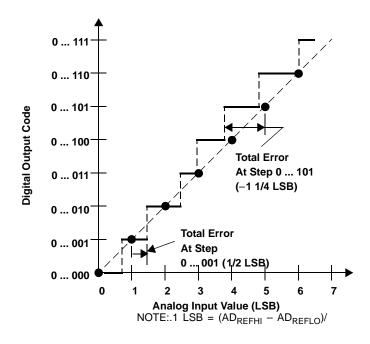


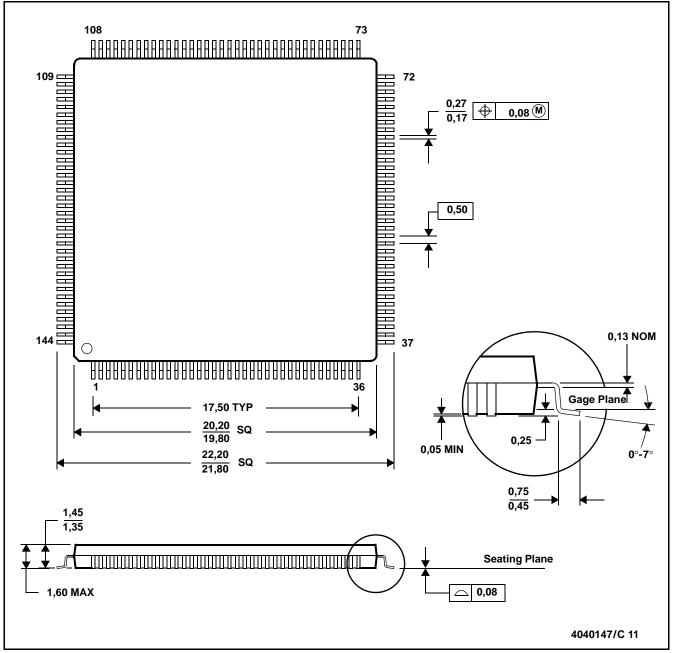
Figure 25. Absolute Accuracy (Total) Error



#### **MECHANICAL DATA**

## PGE (S-PQFP-G144)

#### PLASTIC QUAD FLATPACK



NOTE:. All linear dimensions are in millimeters.

NOTE:. This drawing is subject to change without notice.

NOTE: Falls within JEDEC MS-026.

#### **Thermal Resistance Characteristics**

PARAMETER	°C/W
$R_{\ThetaJA}$	43
R <sub>⊕JC</sub>	5



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## TMS470R1VF48C/VF48B 16/32-BIT RISC FLASH MICROCONTROLLER REVISION HISTORY

### **REVISION HISTORY**

REV	DATE	NOTES	
D	2/06	Updates: Page 16, memory size (x16) for memory selects 5 and 6 updated. Page 35, operating I <sub>CC</sub> current at 48MHz updated to 125mA.	



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